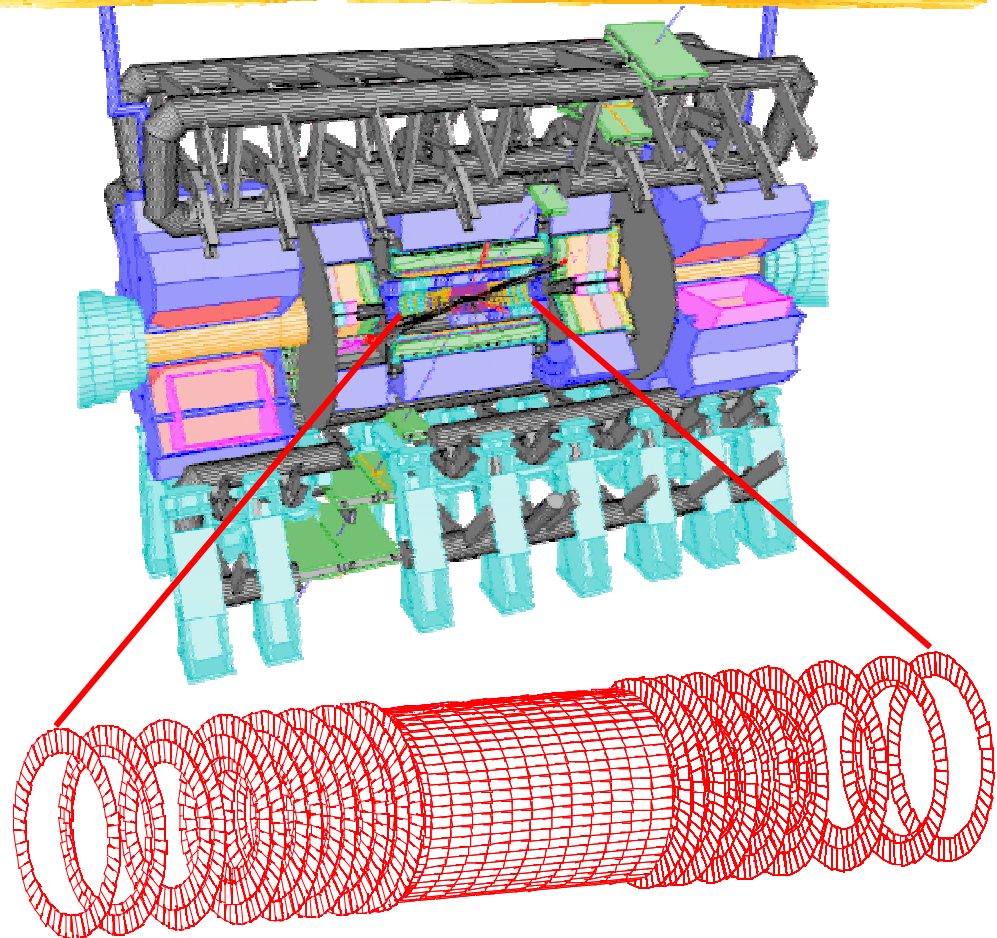




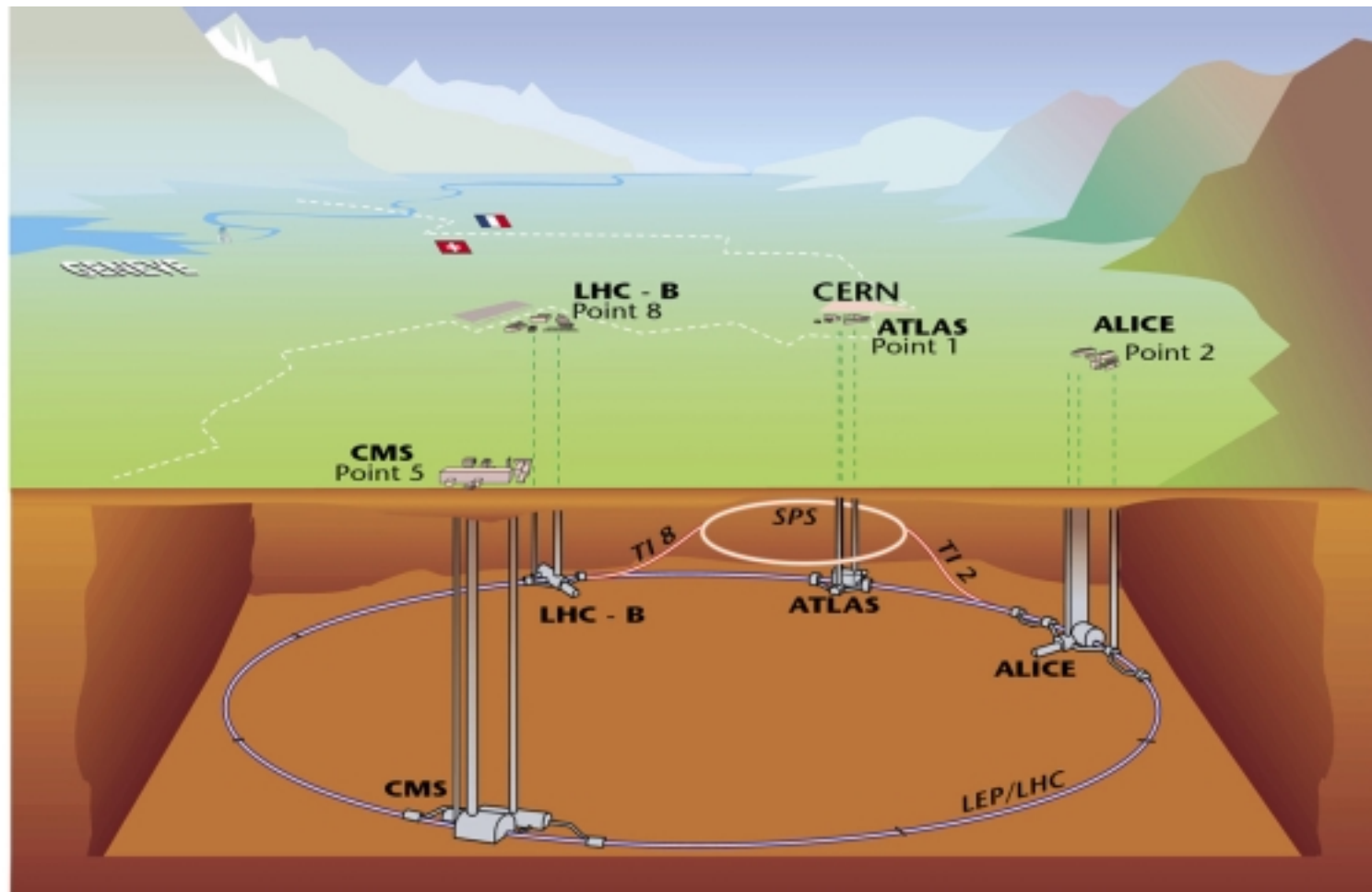
The ATLAS Silicon Microstrip Tracker

Lutz Feld
Freiburg University

- introduction
- system design
- module design
- sensors
- electronics
- hybrids
- module assembly

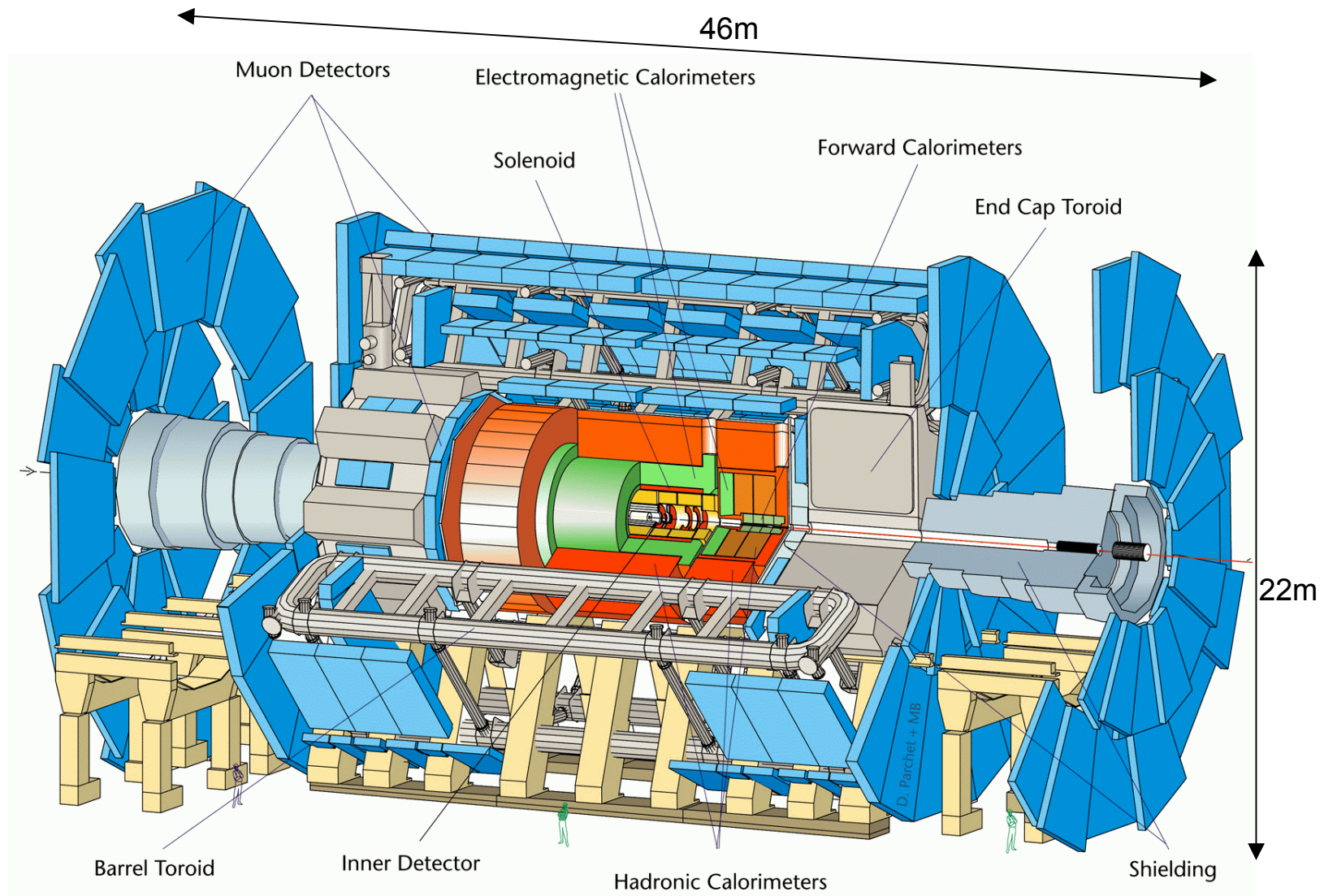


Large Hadron Collider at CERN

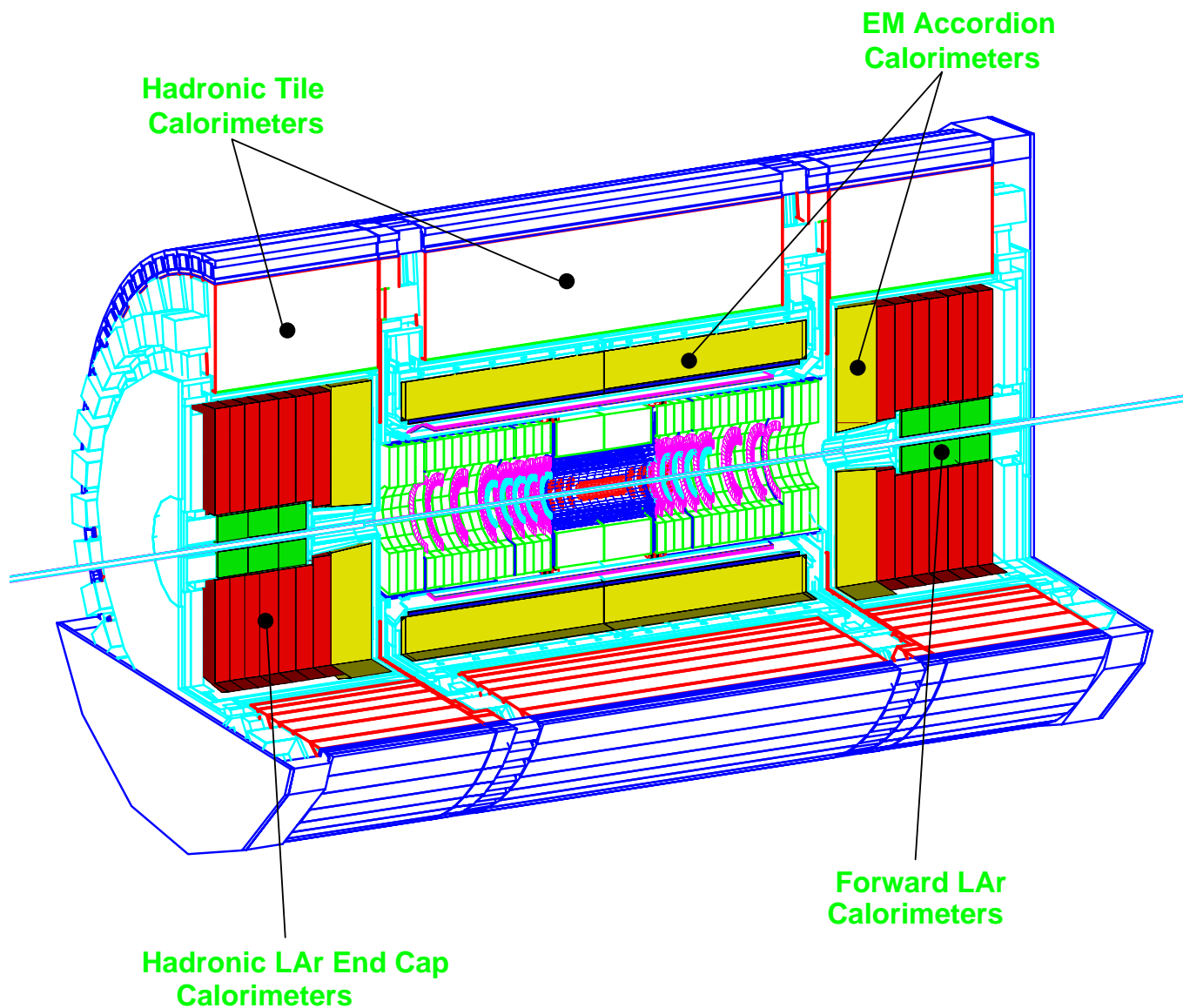


- pp collisions at 14 TeV centre of mass energy
- two multi purpose experiments: ATLAS and CMS
- two specialised experiments: ALICE (heavy ions) and LHC-B (b physics and CP)
- first beam in 2005

ATLAS-Detector



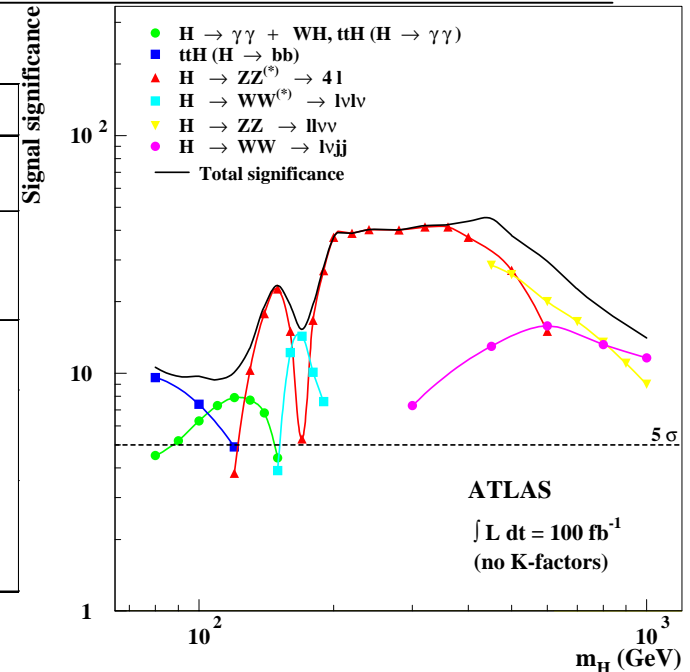
ATLAS without Muon Spectrometer



LHC Physics and its Requirements on the Tracker Performance

○ SM Higgs H^0

higgs mass	explorable decays	tasks for the tracker
<110 GeV	$H^0 \rightarrow b\bar{b}$	<ul style="list-style-type: none"> • secondary vertex tag
80 GeV-150 GeV	$H^0 \rightarrow \gamma\gamma$	<ul style="list-style-type: none"> • isolation of photon candidates • calibration of ECAL • low mass
110 GeV-700 GeV	$H^0 \rightarrow Z Z^{(*)} \rightarrow 2l^+ 2l^-$	<ul style="list-style-type: none"> • measurement of high momentum electrons and muons
150 GeV-200 GeV	$H^0 \rightarrow W^+ W^- \rightarrow l^{+/-} \nu l^{+/-} \nu$	<ul style="list-style-type: none"> • lepton isolation • measurement of high energy jets
300 GeV-1 TeV	$H^0 \rightarrow Z Z \rightarrow l^+ l^- \nu \nu$ $H^0 \rightarrow Z Z \rightarrow l^+ l^- j j$ $H^0 \rightarrow W^+ W^- \rightarrow l^{+/-} \nu j j$	



○ MSSM Higgs $H^{\pm}/, h, H, A$:

- Many decays give signatures similar to the SM higgs decays, but in addition t and b final states are important,
- therefore **impact parameter resolution**, recognition of **secondary vertices** in high energy jets and **track isolation** are important.

○ Supersymmetric Particles:

- Depending on SUSY parameters decays to final states with many b's or many μ 's are expected.

○ b-Physics (CP Violation, Oscillations, B_c , ...):

- Obviously **impact parameter resolution** (2D and 3D) and **secondary vertexing efficiency and purity** are important.

Silicon Tracking is very powerful at hadron colliders: top quark discovery as seen by CDF

e + 4 jet event

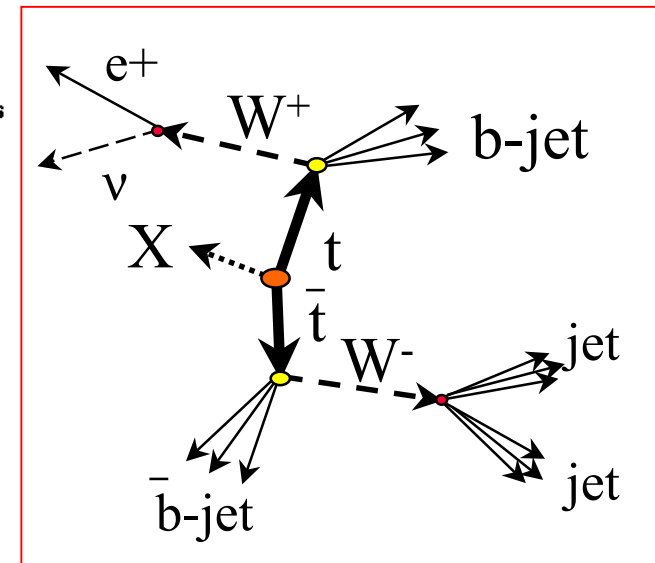
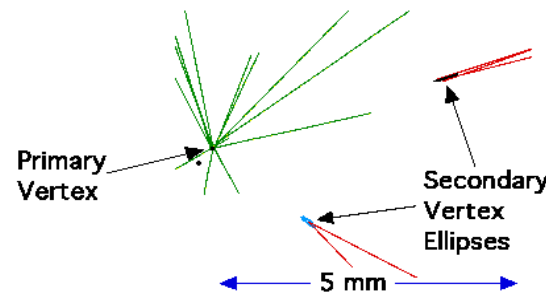
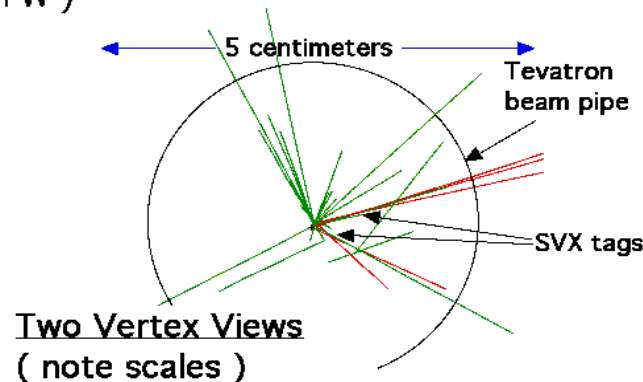
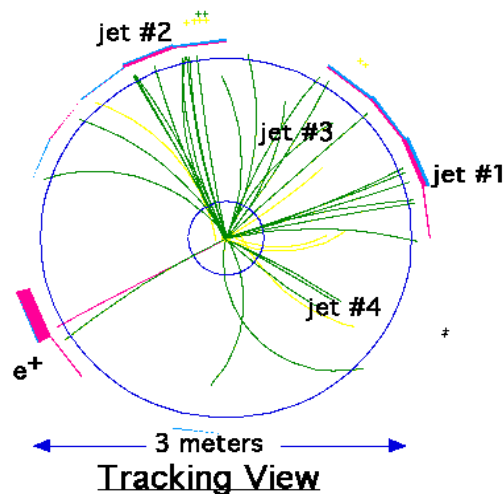
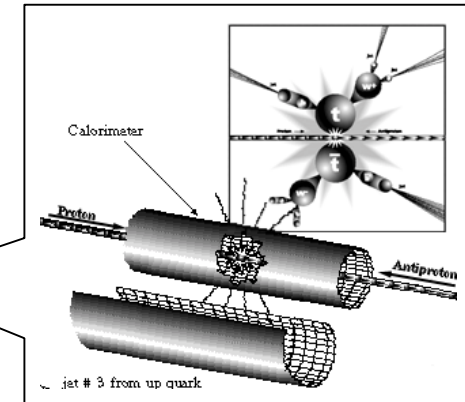
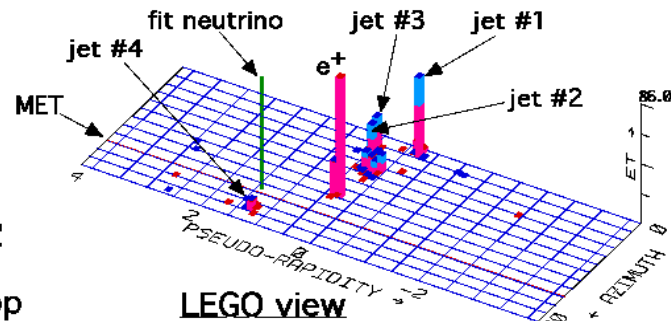
40758_44414

24-September, 1992

TWO jets tagged by SVX

fit top mass is $175 \pm 10 \text{ GeV}/c^2$

e^+ , Missing E_t , jet #4 from top
jets 1,2,3 from top (2&3 from W)

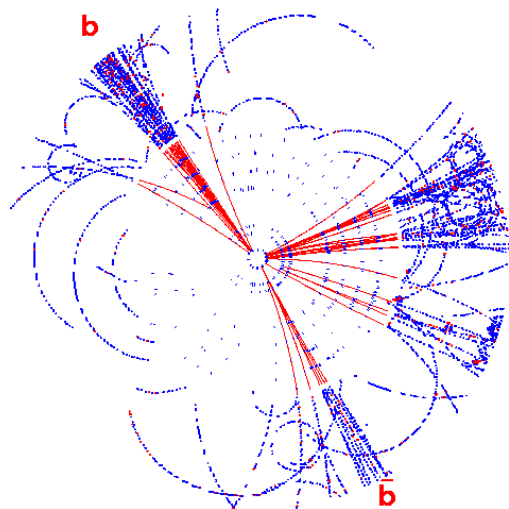


LHC means high rate and high multiplicity

at full luminosity $L=10^{34} \text{ cm}^{-2} \text{ s}^{-1}$:

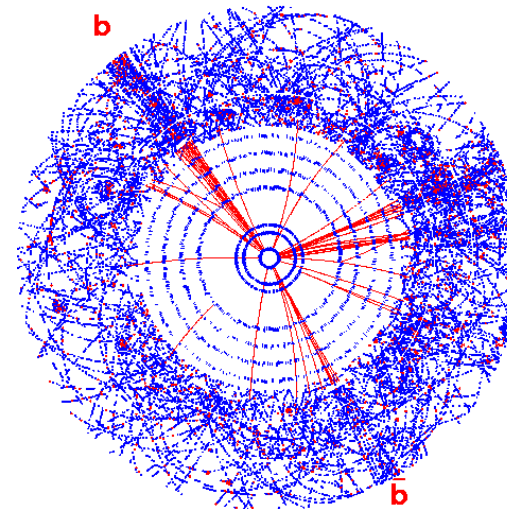
- ~23 overlapping interactions in each bunch crossing (every 25 ns)
- event rate of ~1GHz needs to be reduced to ~100Hz written to tape => reduction of 10^7
- ~6.5 charged particles per unit of rapidity in average collision
- => inside tracker acceptance ($|\eta|<2.5$) 750 charged tracks (plus ~375 neutrals) per bunch crossing
- per year: $\sim 5 \times 10^{14}$ bb; $\sim 10^{14}$ tt; ~20,000 higgs; $\sim 10^{16}$ inelastic collisions

a $H \rightarrow b\bar{b}$ event

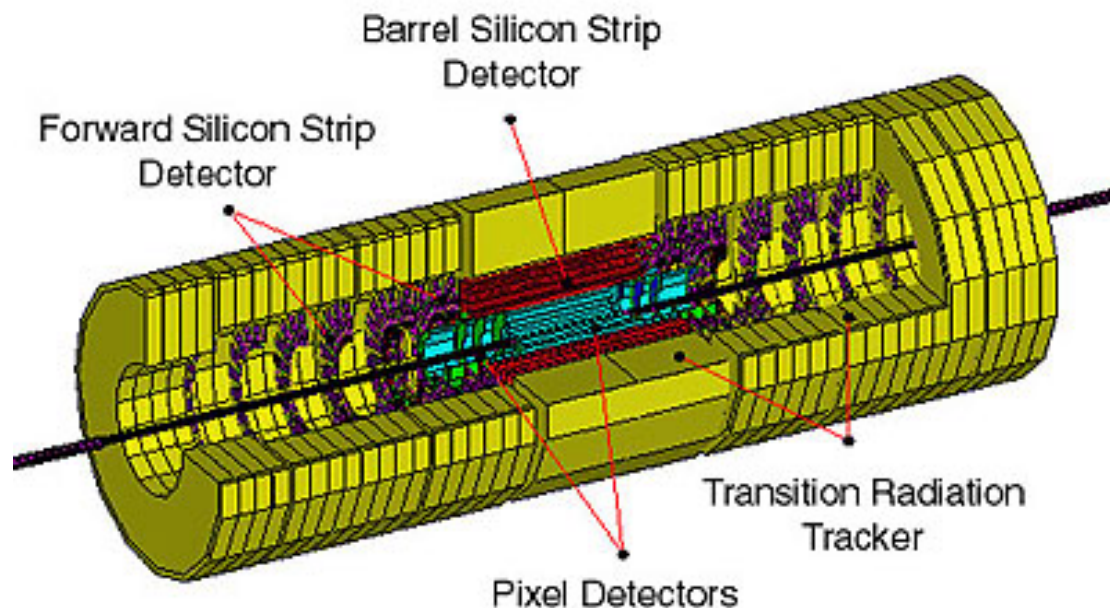


plus 22 minimum bias interactions

a $H \rightarrow b\bar{b}$ event as observed at high luminosity



ATLAS Inner Tracker



High flux environment:

at $L=10^{34}\text{cm}^{-2}\text{s}^{-1}$ **~1000 particles per 25 ns** inside the acceptance of the tracker from about 20 proton proton collisions.

Requires detector techniques which ensure

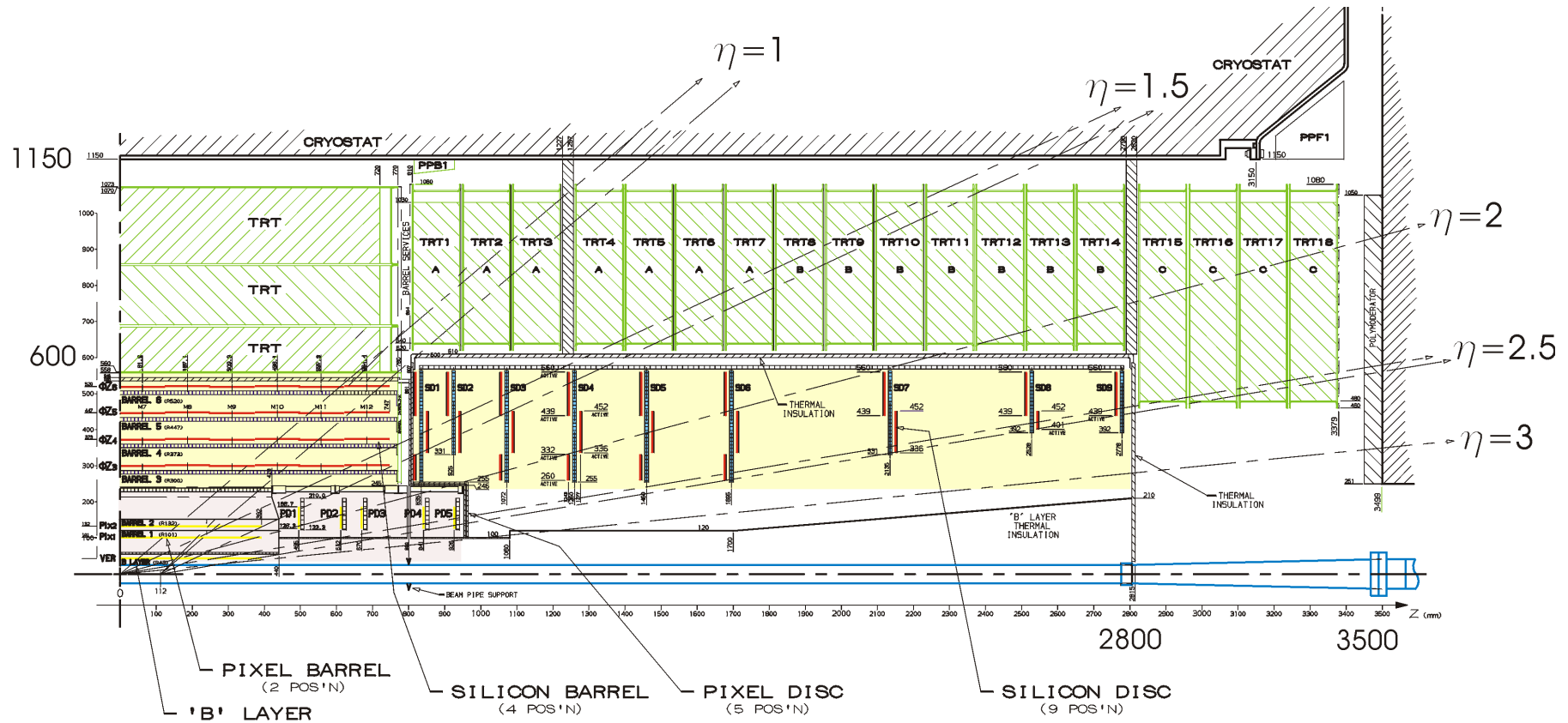
- **low occupancy** -> high granularity
 - **read-out speed** -> fast detectors
 - **radiation tolerance** -> radiation hardness
- this has to be balanced with the cost for large sensor areas.

Performance:

- rapidity coverage: $|\eta| < 2.5$
- momentum resolution for isolated leptons:
 $\Delta p_T / p_T \sim 0.1 p_T (\text{TeV})$
- track reconstruction efficiency (high- p_T)
 - for isolated tracks $\epsilon > 95\%$,
within jets $\epsilon > 90\%$,
 - ghost tracks $< 1\%$ (for isolated tracks)
- **impact parameter** resolution at high- p_T
 $\sigma_{r-\phi} < 20 \mu\text{m}$, $\sigma_z < 100 \mu\text{m}$
- **low material** budget for tracker and ECAL performances
- **lifetime** > 10 LHC years

system		area (m ²)	resolution (μm)	channels (10 ⁶)	$ \eta $ coverage
pixel	1 b layer	0.2	RF=12, z=66	16	2.5
	2 barrels	1.4	RF=12, z=66	81	1.7
	2x5 disks	0.7	zF=12, R=77	43	1.7-2.5
	total	2.3		140	2.5
SCT	4 barrels	34.4	RF=16, z=580	3.2	1.4
	2x9 disks	26.7	zF=12, R=580	3.0	1.4-2.5
	total	61.1		6.2	2.5
TRT	barrel (36)		170 per straw	0.1	0.7
	end-caps		170 per straw	0.32	0.7-2.5
	total			0.42	2.5

ATLAS Inner Tracker

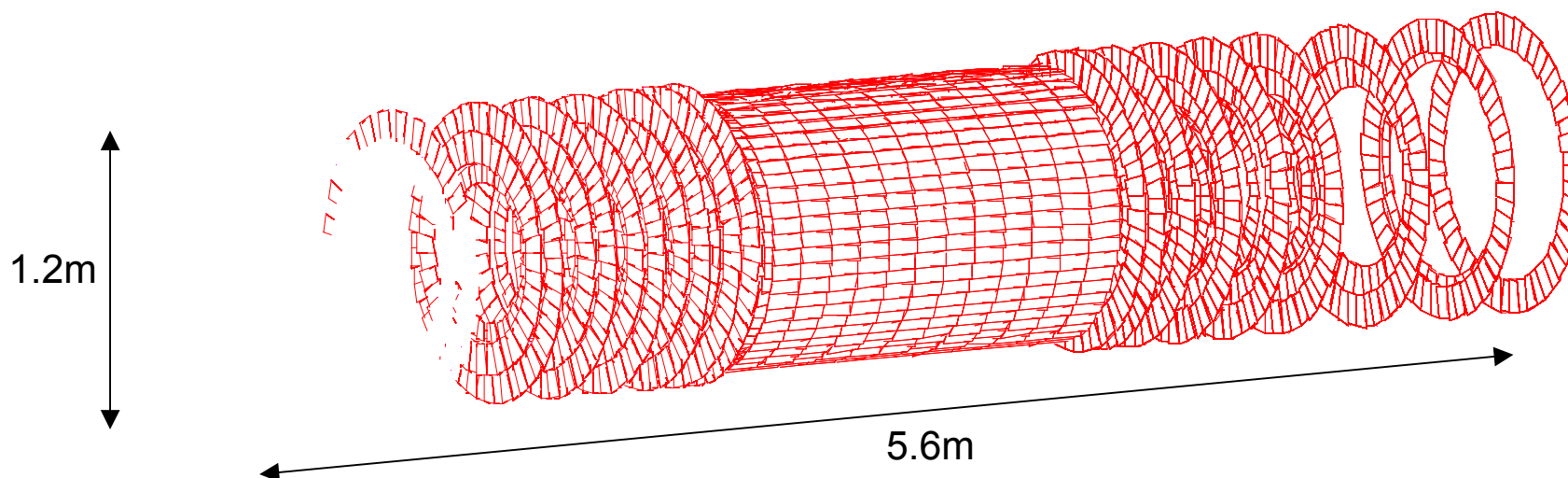


ATLAS INNER TRACKER GEOMETRY
(1-TB-0035-060-U 27MAY98)

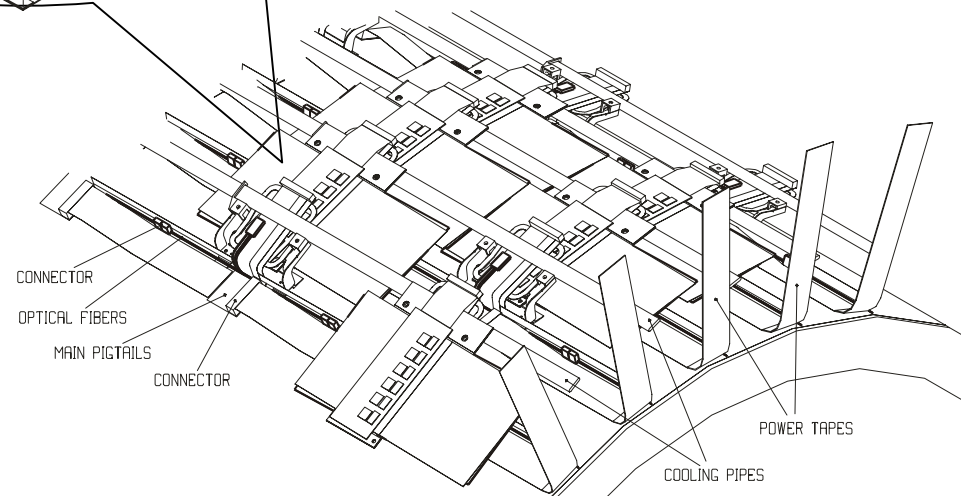
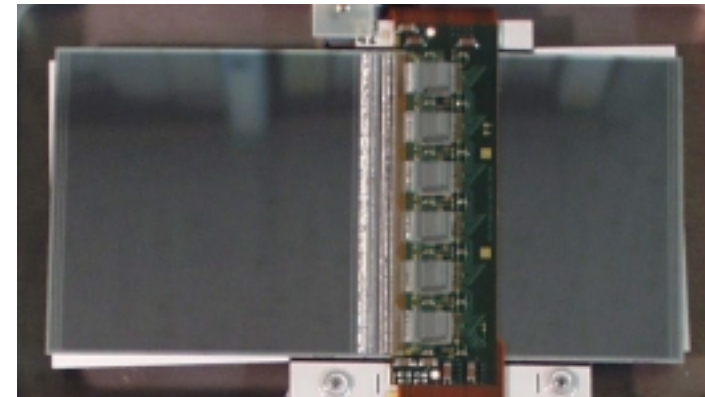
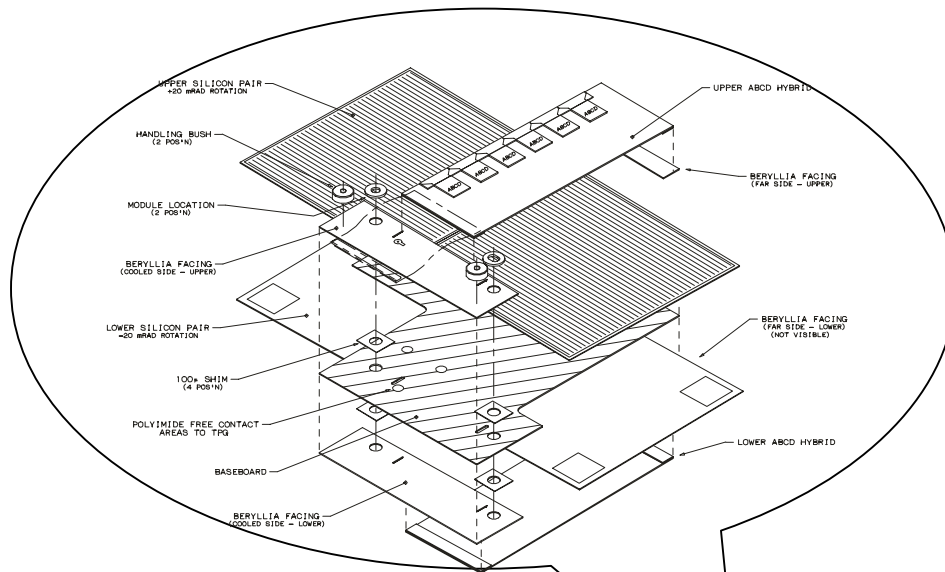
geom_U_1

ATLAS Silicon Microstrip Tracker SCT

- 4 barrel layers
 - barrel radii: 300, 371, 443 and 514 mm; length 1600 mm
 - in total 2112 modules
- 2 x 9 forward disks
 - disk distance from $z = 0$: 835 - 2788 mm, radii: 259-560 mm
 - in total 1976 modules (3 rings: 40, 40, 52 modules each)
- all 4088 modules double side
- 15,392 sensors of total 61.1m^2
- total length of diode: 716 km
- 49,056 front-end chips of total 6.3 Mio. channels

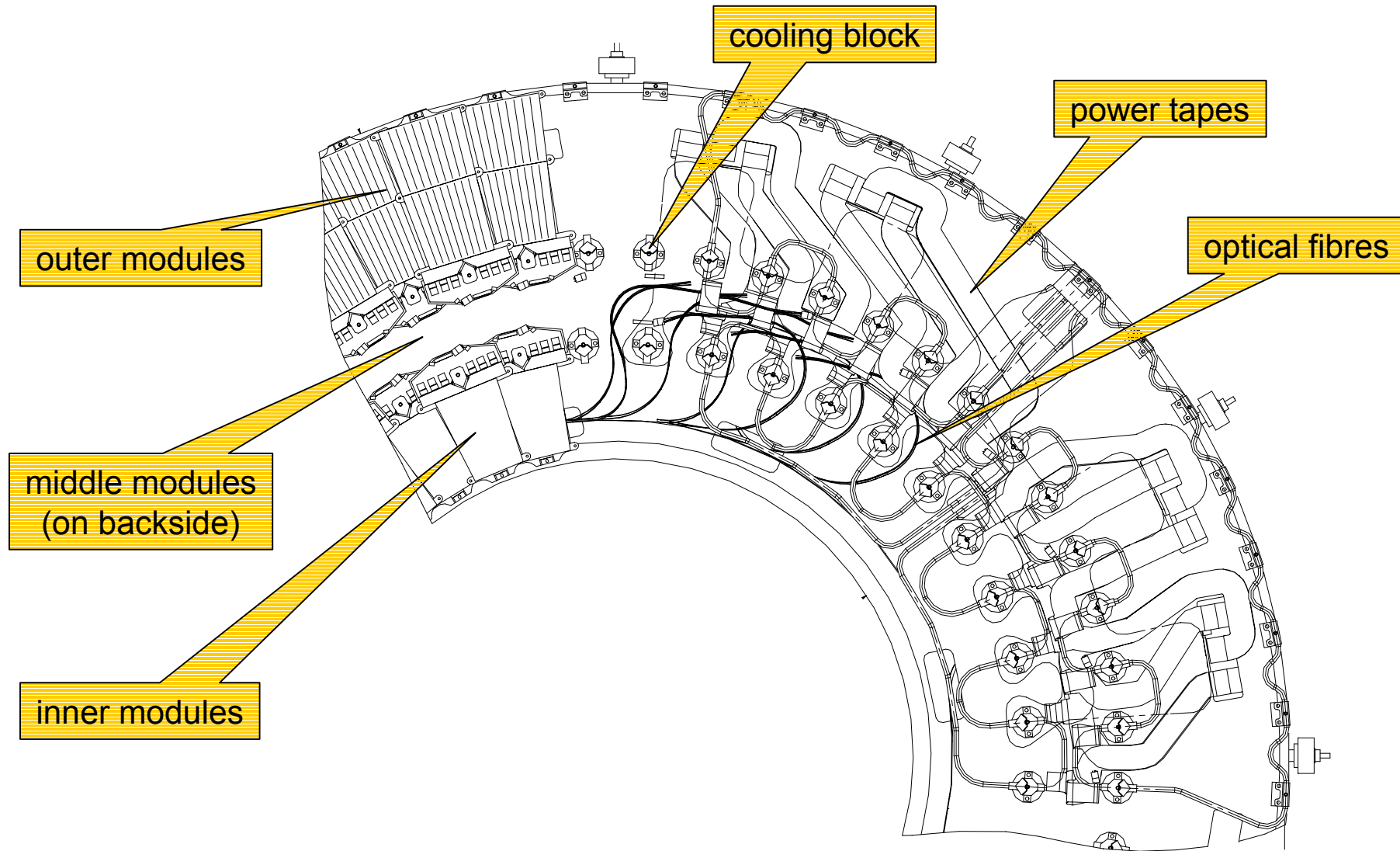


Barrel Modules

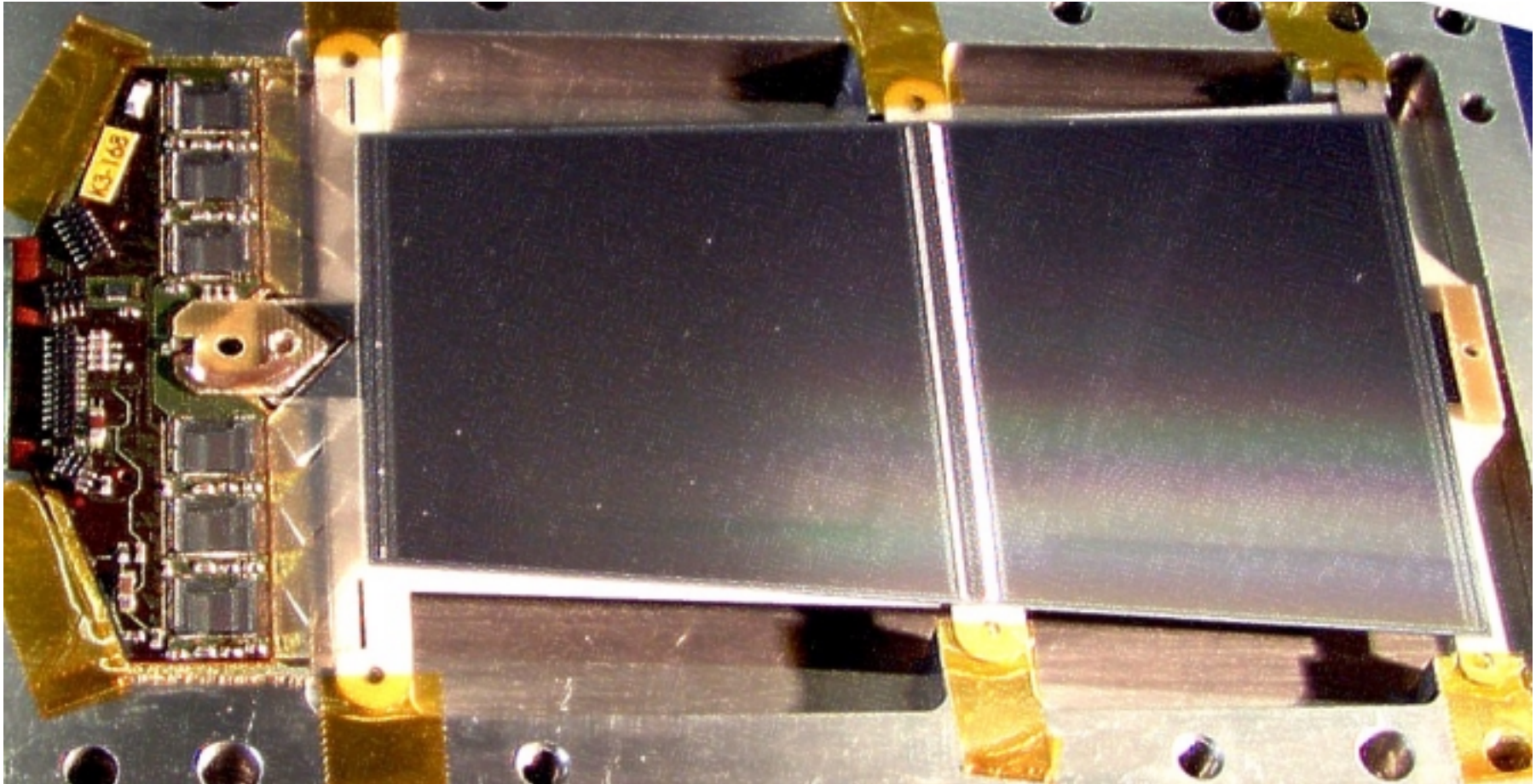


- double sided module as back-to-back build-up of 2 pairs of rectangular sensors
- 40 mrad stereo angle to measure second co-ordinate
- centre-tapped electronics hybrid

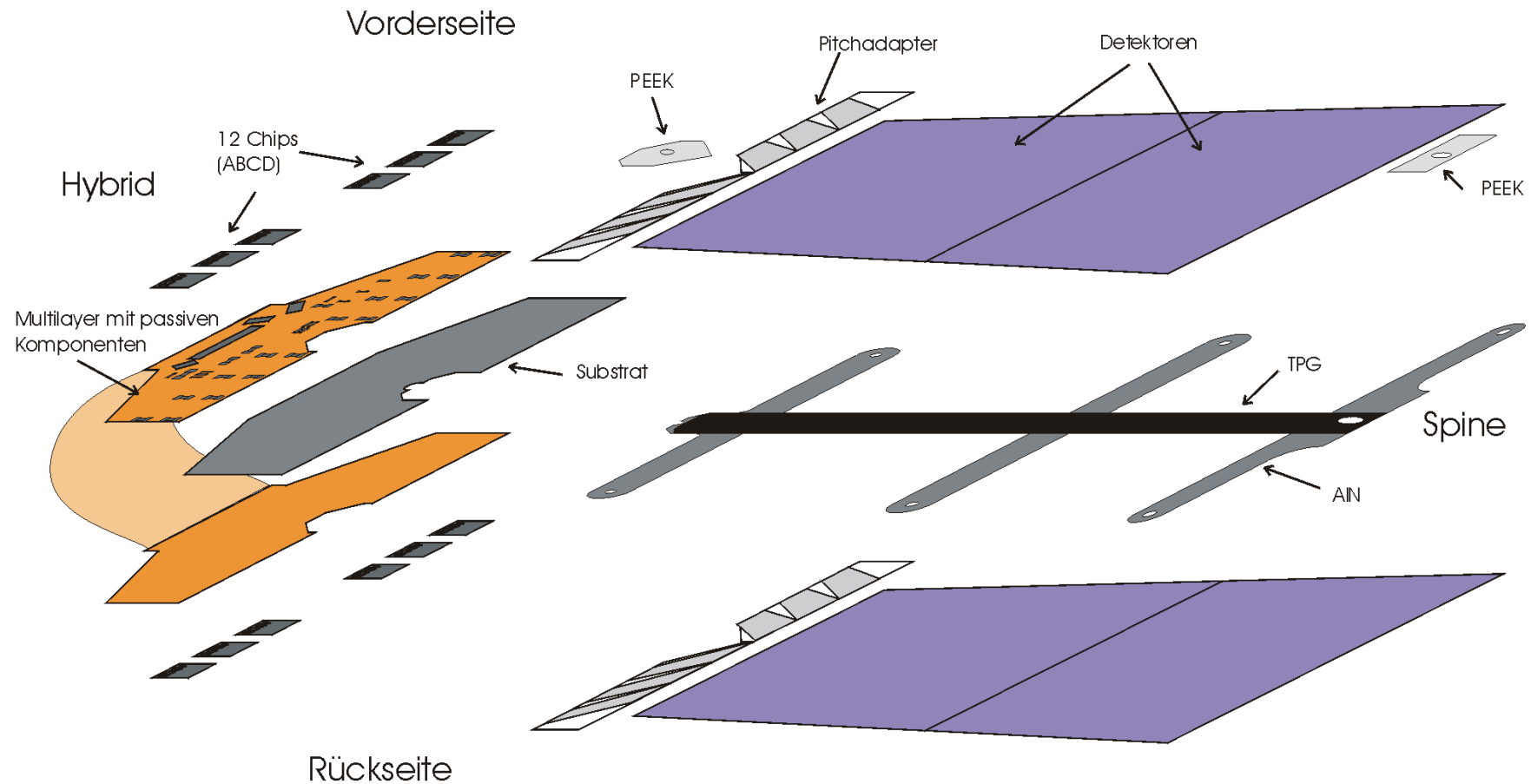
SCT Forward Disk



Forward Module in Transport Frame



Forward Module



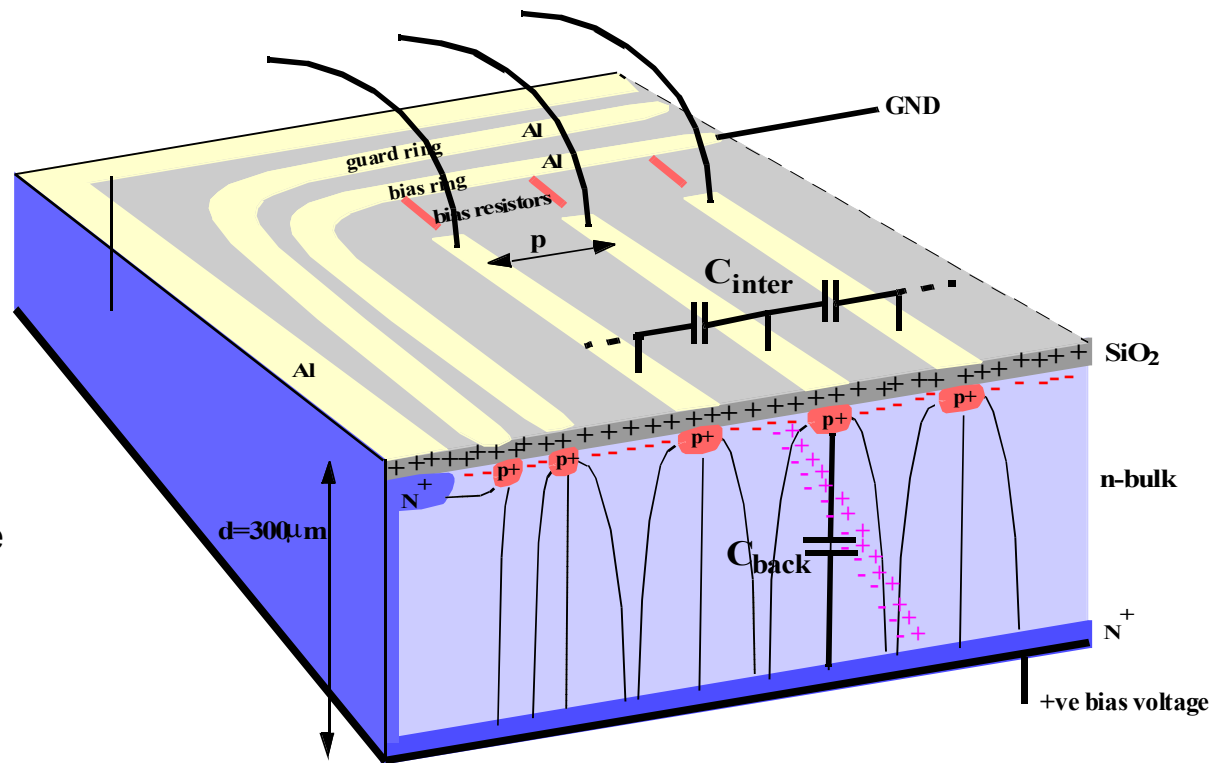
- double sided module as back-to-back build-up of 2 pairs of wedge shaped sensors
- 40 mrad stereo angle to measure second co-ordinate
- double sided, end-tapped electronics hybrid
- alignment: 4 μ m sensor-to-sensor on each side, 8 μ m front-to-back

Silicon Microstrip Detector

- **principle:** collection of charge released in the depleted volume of a reverse biased diode
- spatial resolution through segmentation of diode
- p strips on n substrate
- AC coupling to keep leakage current away from read-out electronics
- biasing through polysilicon or implanted resistors

properties

- leakage current
- depletion voltage and substrate resistivity
- high voltage stability
- interstrip capacitance
- backplane capacitance
- crystal orientation
- charge collection
- signal to noise



Radiation Environment

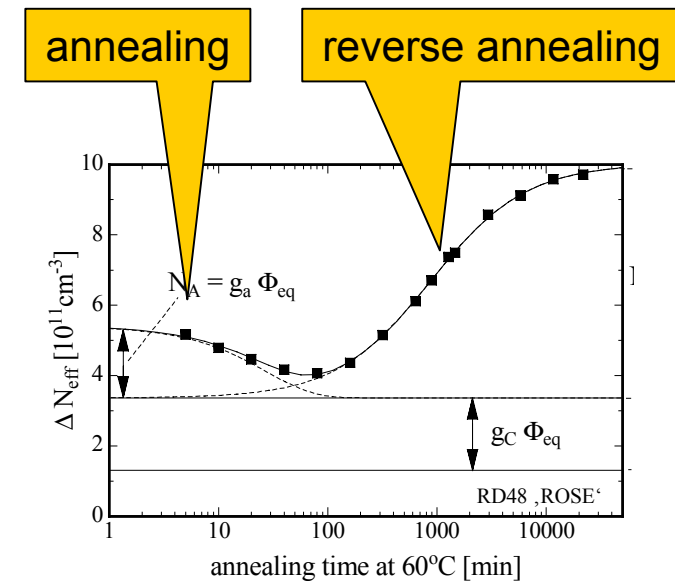
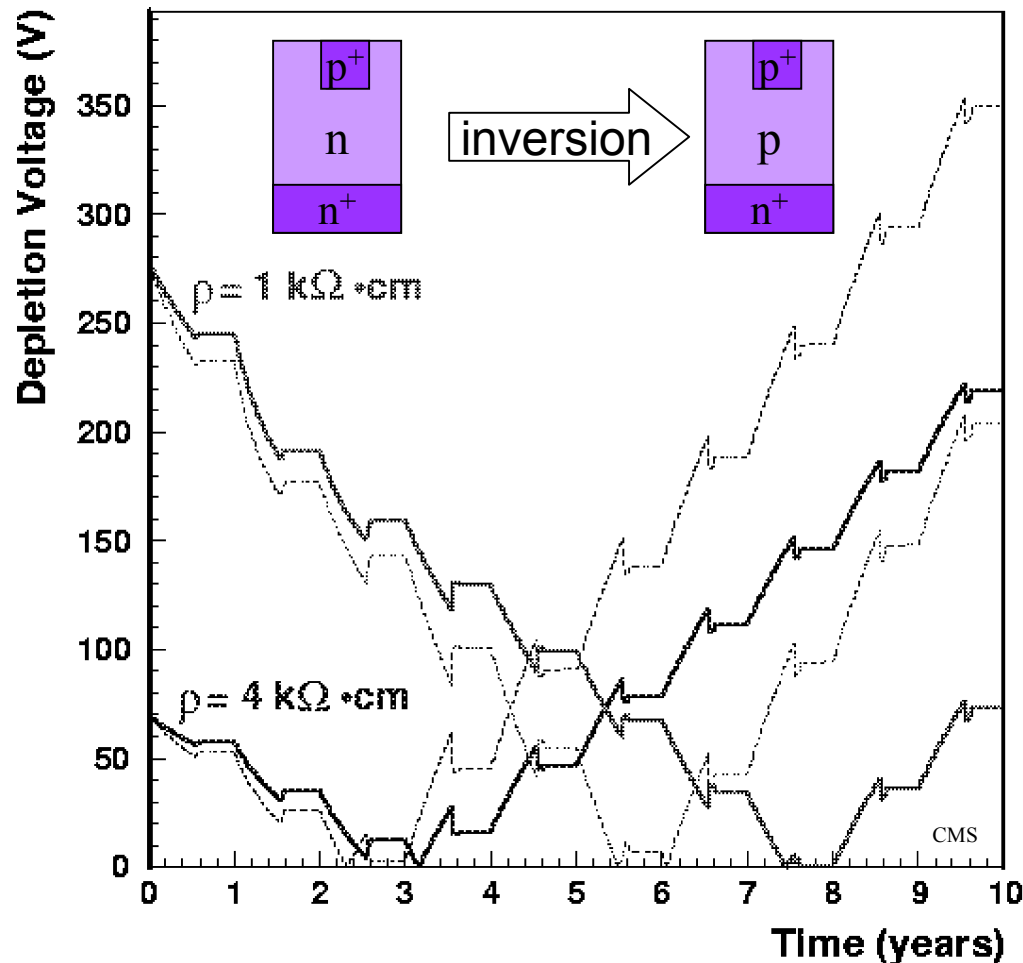
- tracking detectors at the LHC are subject to a significant amount of irradiation by charged particles and neutrons
- in SCT volume up to **1.2×10^{14} 1-MeV-n/cm² for 10 years** of LHC running
- **major challenge for the system design**
- **damage to sensors**
 - **bulk damage:** displacement of Si atoms from lattice sites
 - creation of energy levels in the band gap: **increases leakage current** $I_{\text{leak}} \sim \text{fluence}$
 - deep levels act as acceptors: **inversion from n-type to p-type and depletion voltage changes**
 - radiation induced energy levels act as traps: **deterioration of charge collection**
 - **surface damage:** creation of charge carriers in silicon oxide
 - modification of electron accumulation layer and change of interstrip capacitance
- **damage to electronics**
 - modification of oxide charge changes threshold voltages of MOS transistors
 - parasitic currents
 - single event upset
- **damage to other material**
 - deterioration of mechanical properties
 - creation of radicals
 - induced radioactivity

Depletion Voltage

Depletion Voltage V_{dep} and Substrate Resistivity ρ

$$V_{\text{dep}} = (e d^2 N_{\text{eff}}) / (2 \epsilon_0 \epsilon_{\text{Si}})$$

$$N_{\text{eff}} = 1 / (q_e m_e \rho)$$

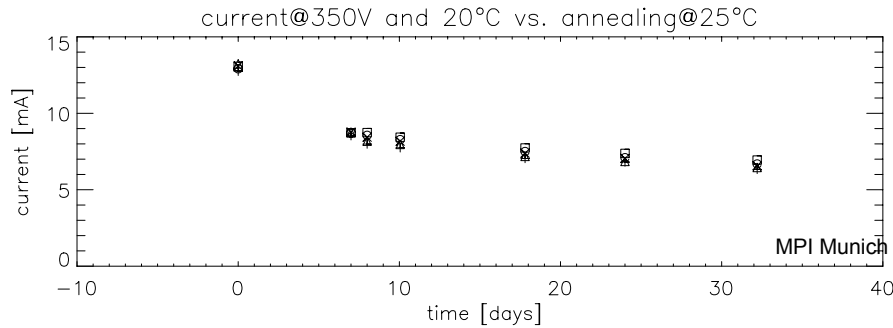


- annealing rate is strongly temperature dependent
- reverse annealing is suppressed at $T < 0^\circ \text{C}$

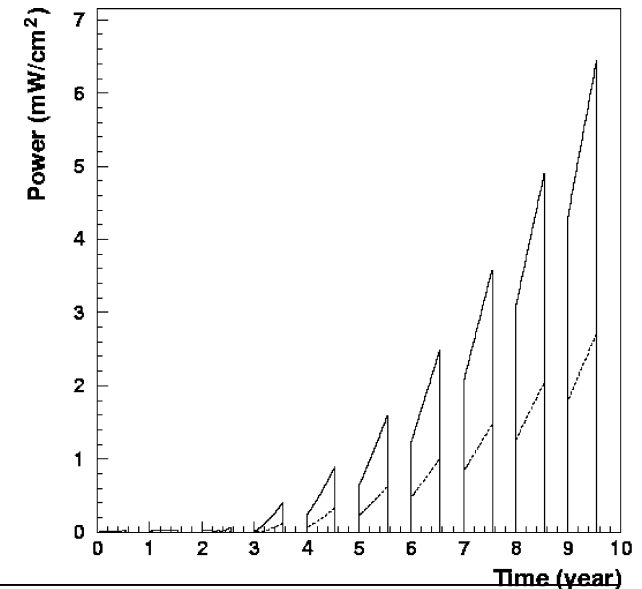
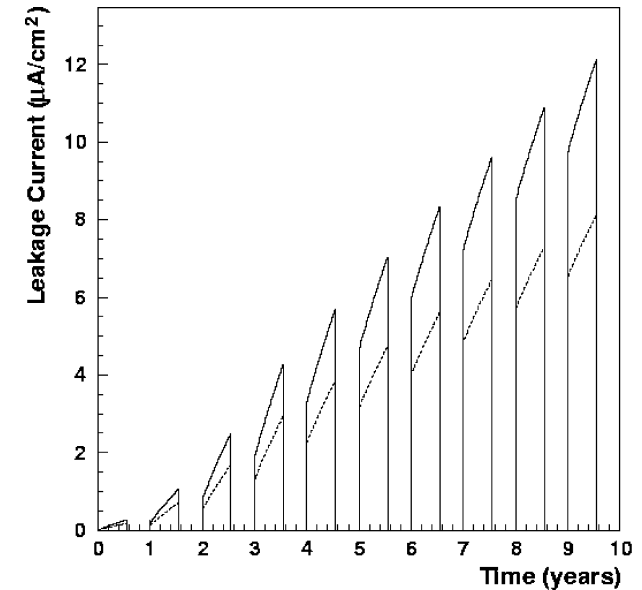
Leakage Current

- $I_{\text{leak}} = \alpha_{\infty} \times \text{volume} \times \text{fluence}$
 - $\alpha_{\infty} \approx 3 \times 10^{-17} \text{ A/cm}$ at 20 °C, fluence in 1MeV equiv.
 - independent of material or radiation type

- beneficial annealing has a significant effect

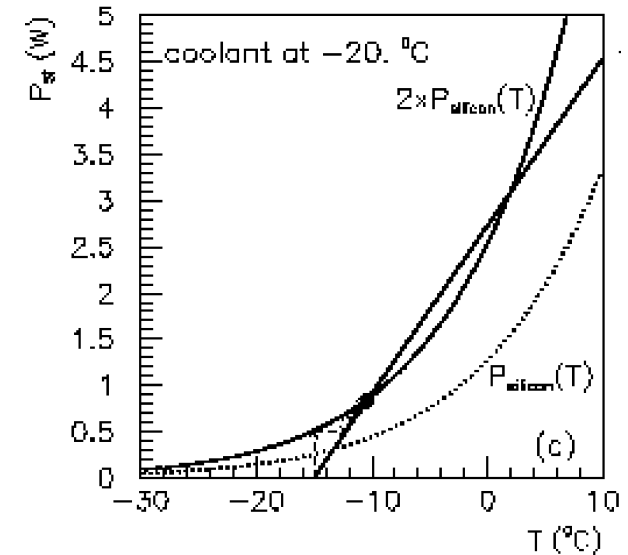
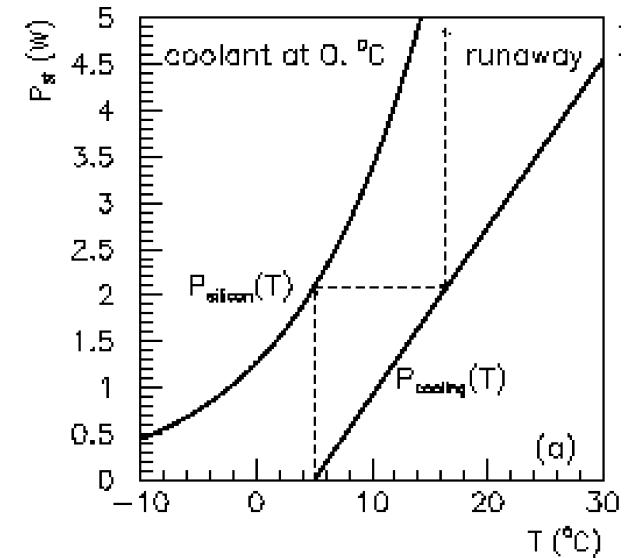
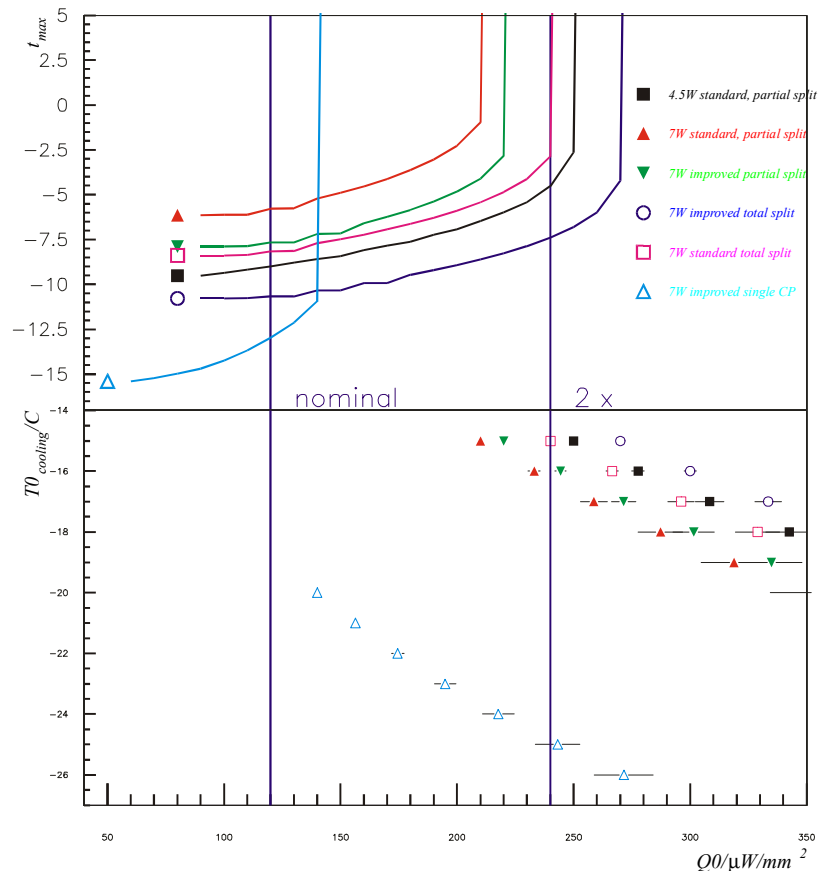


- after 10 years of LHC running:
 - a 12 cm long strip at 100 mm pitch draws ~1 μA ,
 - a detector module (160 cm^2) draws ~2mA,
 - both at -10 °C.
- given the high bias voltage this leads to a significant power dissipation of the silicon itself
 - > need efficient cooling to avoid **thermal runaway**



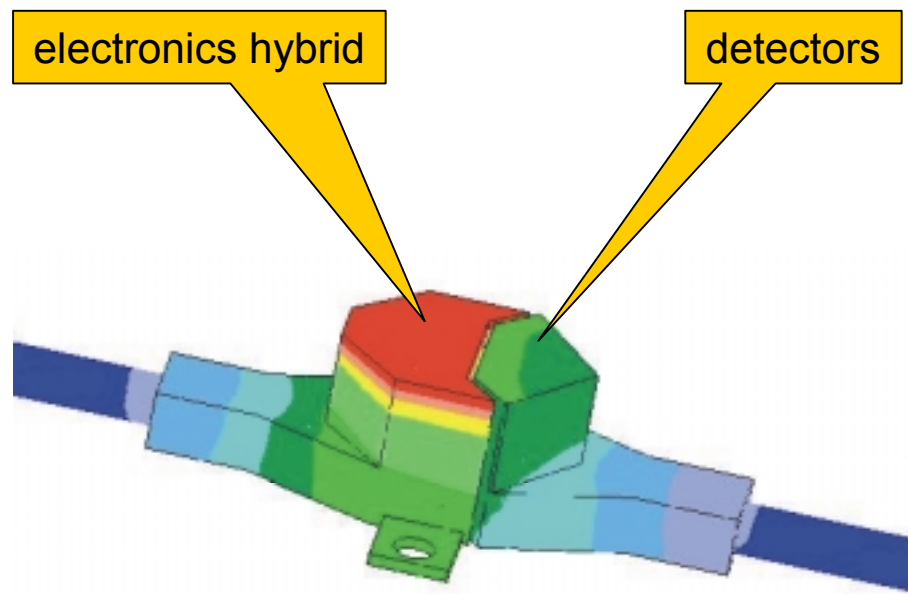
Thermal Runaway

- leakage current strongly temperature dependent
 - $I = I_0 T^2 \exp(-E_g/kT)$
 - current doubles every 7°C.
- large depletion voltages (>350 V)
- after 3×10^{14} p/cm²: 120 μW/mm² at 0 °C
- design requirement: stable operation up to 240 μW/mm²



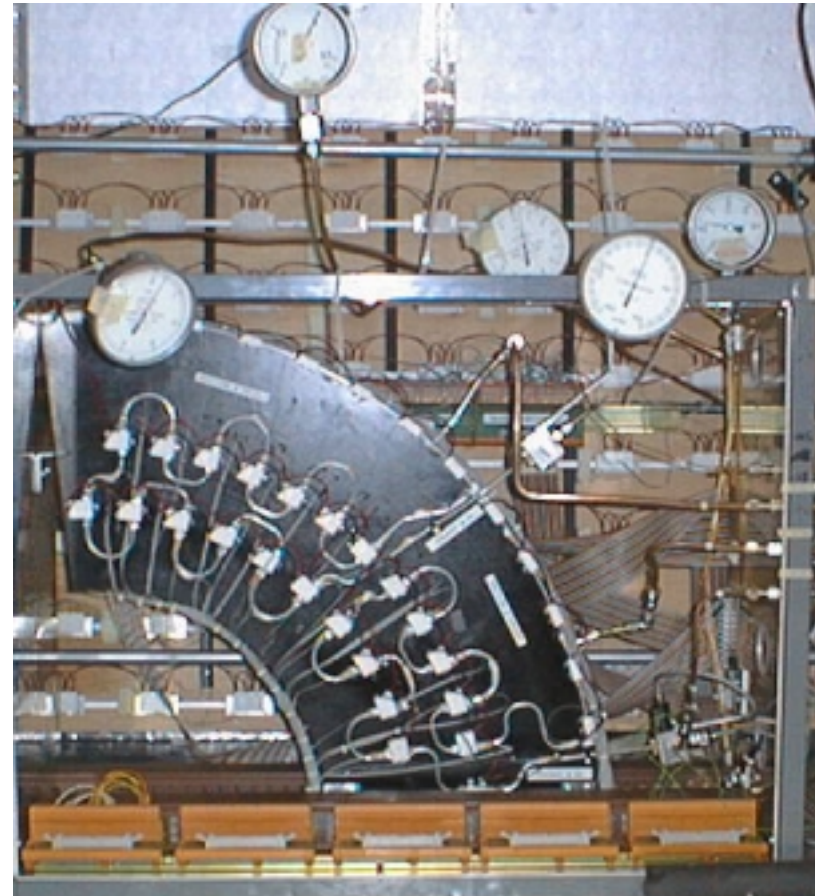
Thermal Split

- modules and cooling blocks designed to separate electronics power dissipation from silicon
- power dissipation of electronics hybrid ~ 7.5 W
- power dissipation of detectors after 10 years running ~ 1 W



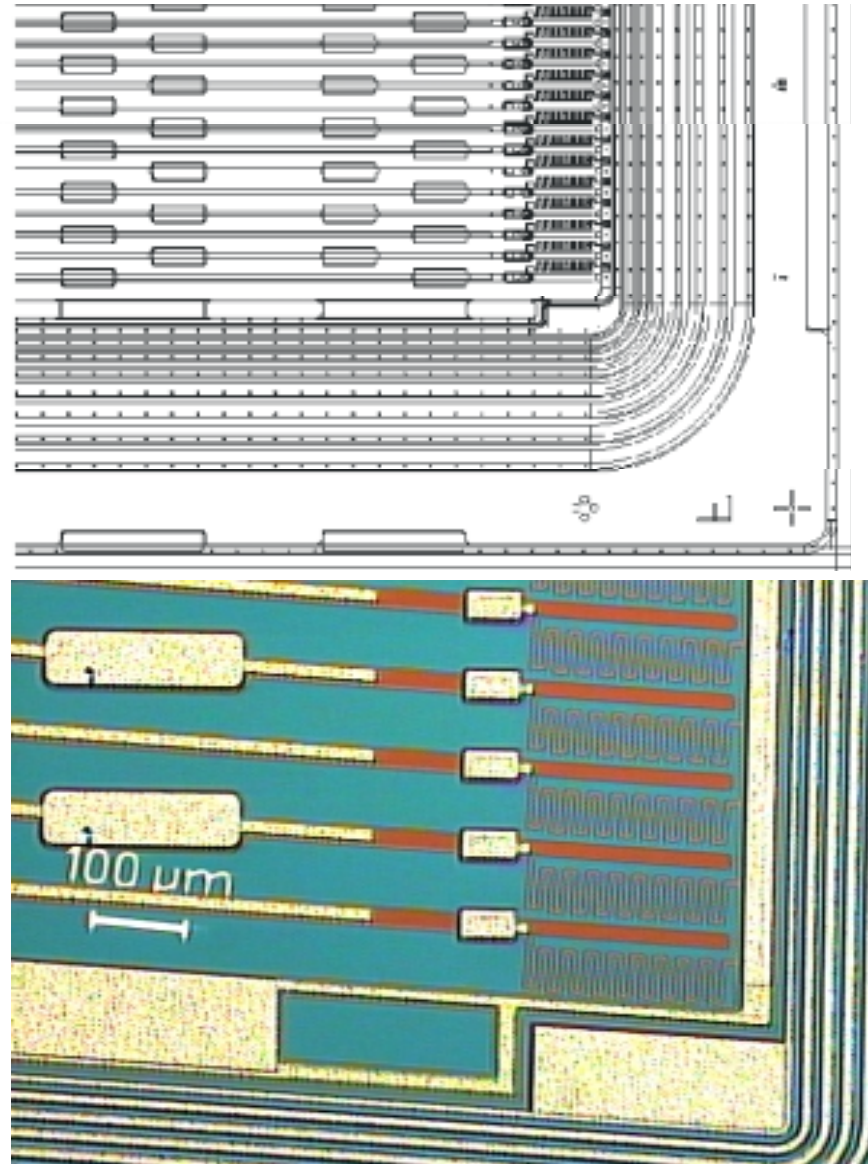
Cooling System

- C_3F_8 evaporative cooling system
- better heat removal per unit mass flow compared to monophasic system (use evaporation)
->use fewer and smaller diameter pipes, warm input pipe
- input pressure ~8bar,
in cooling manifold ~1.5 bar
- operating temperature ~-20°C
- cooling system tested ok on several test structures (picture)
- measurements on modules agree with thermal simulations



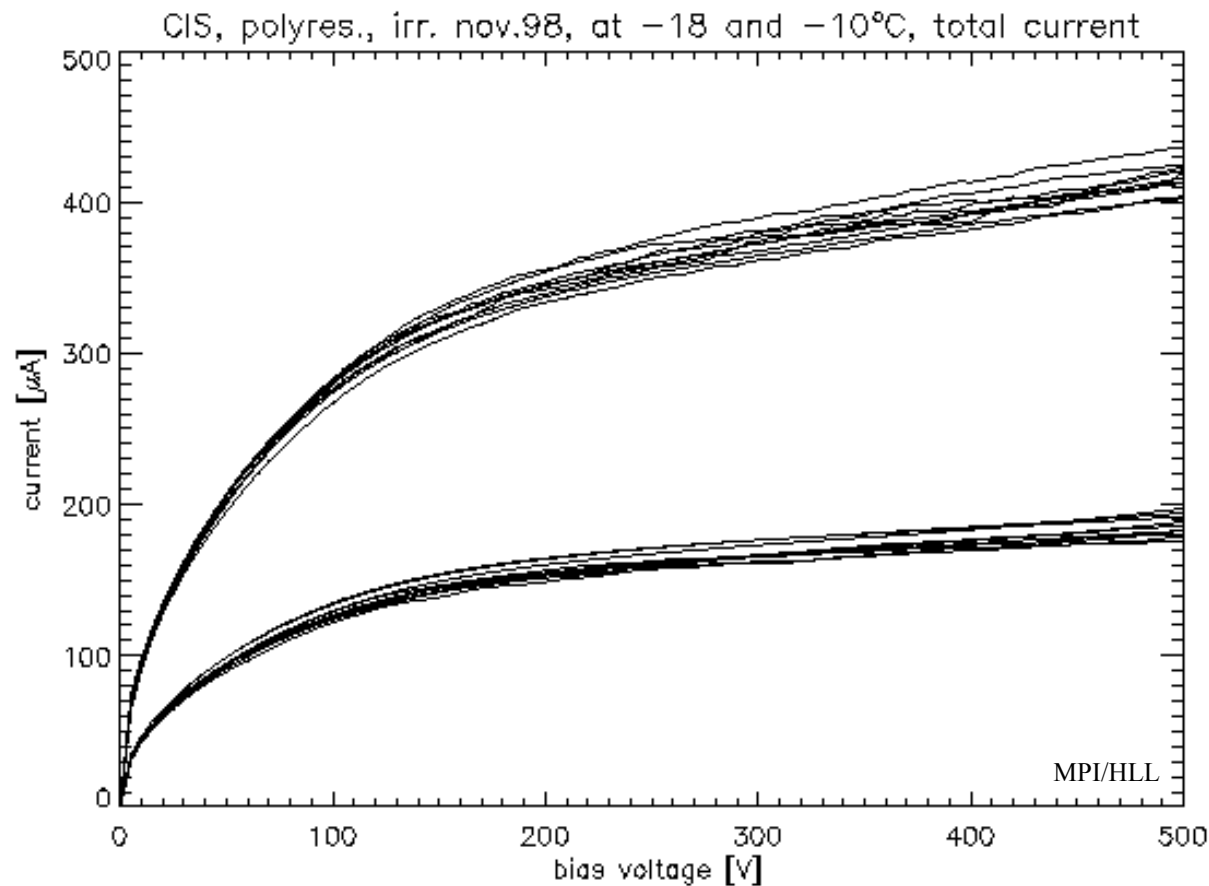
ATLAS SCT Sensors

- p-on-n single sided detectors
- 285 μm thick
- 2-8 k $\Omega\cdot\text{cm}$
- 4" substrate
- barrel
 - 64x64mm²
 - 80 μm pitch
- forward
 - 5 different wedge shaped sensors
 - radial strips
 - 50...90 μm pitch
- 768 read-out strips
- AC coupled to read-out
- polysilicon or implanted resistors
- multiguard structure for HV stability
- ~20000 sensors needed
- ordered from Hamatsu, CIS and Sintef

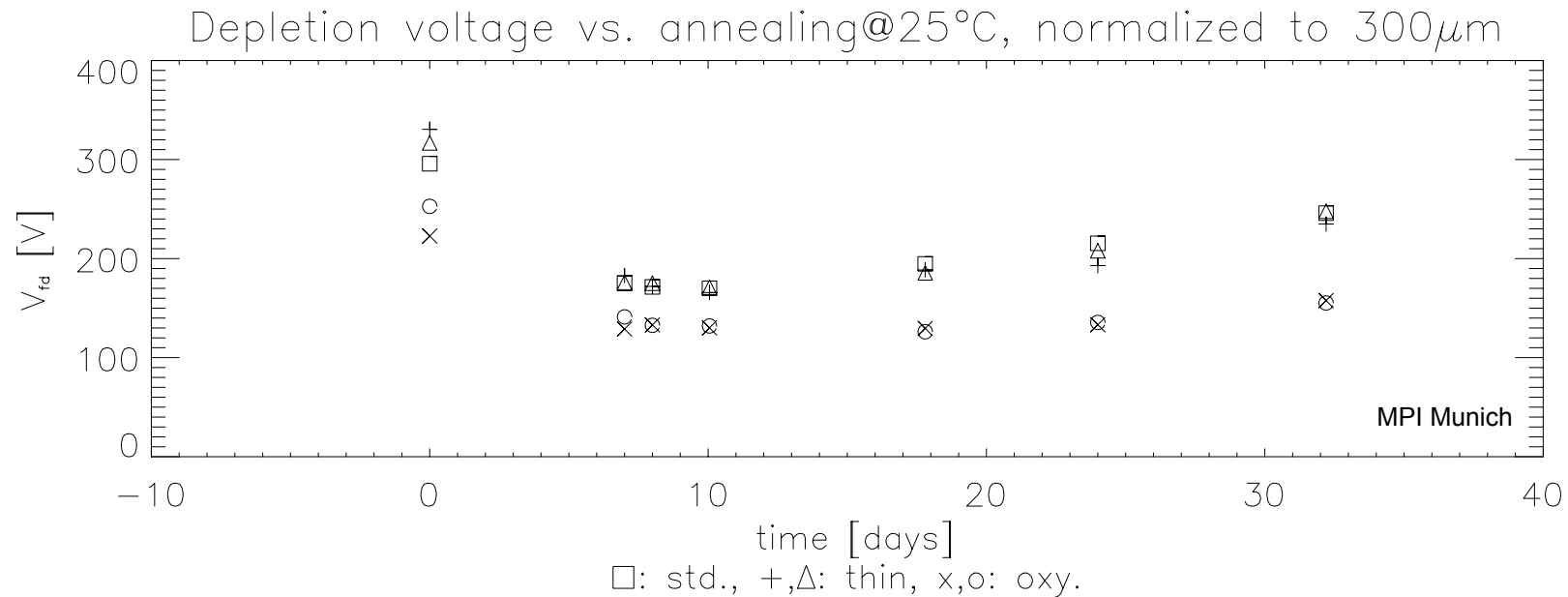


IV after Irradiation

- IV curves for CIS wedge detectors after 3×10^{14} p/cm² (7 days annealing at 25°C)
- Spec: <250 mA @ 450V @ -18 C



Depletion Voltage after Irradiation

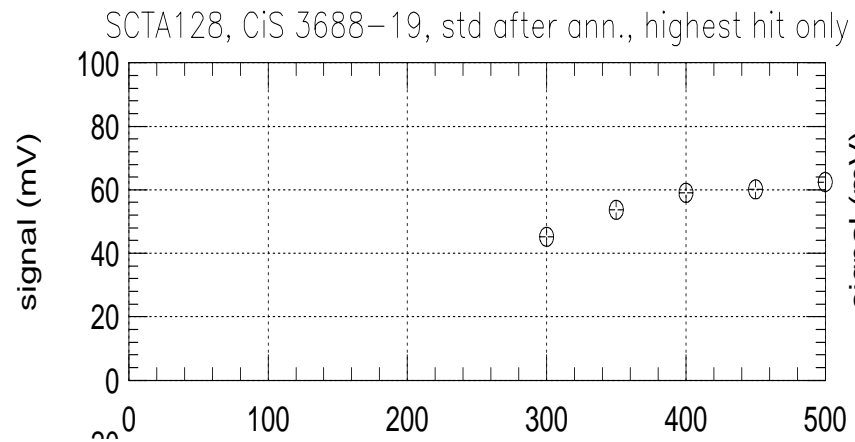


- **beneficial annealing: few days at room temperature decreases depletion voltage**
- **reverse annealing: longer time at temperatures $>0^{\circ}\text{C}$ increases depletion voltage**
- **-> need to keep irradiated silicon cold ($<0^{\circ}\text{C}$)**
- **oxygenated detectors: less damage and slower reverse annealing**

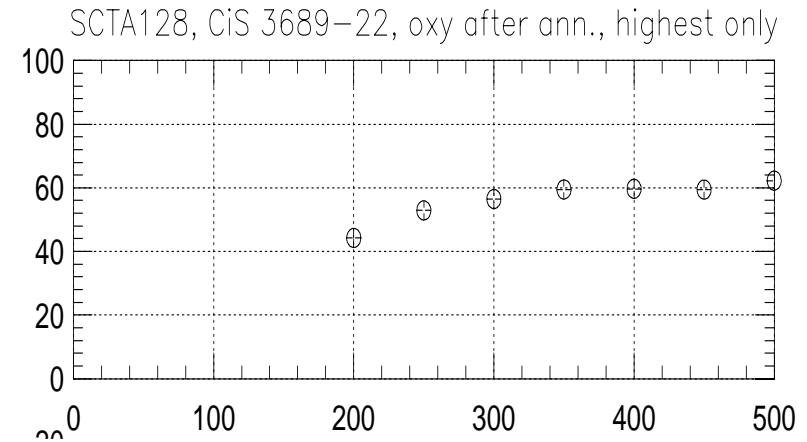
Charge Collection Efficiency

sensors irradiated to 3×10^{14} 24GeV-p/cm²

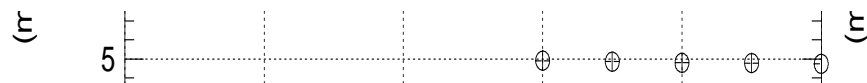
standard material



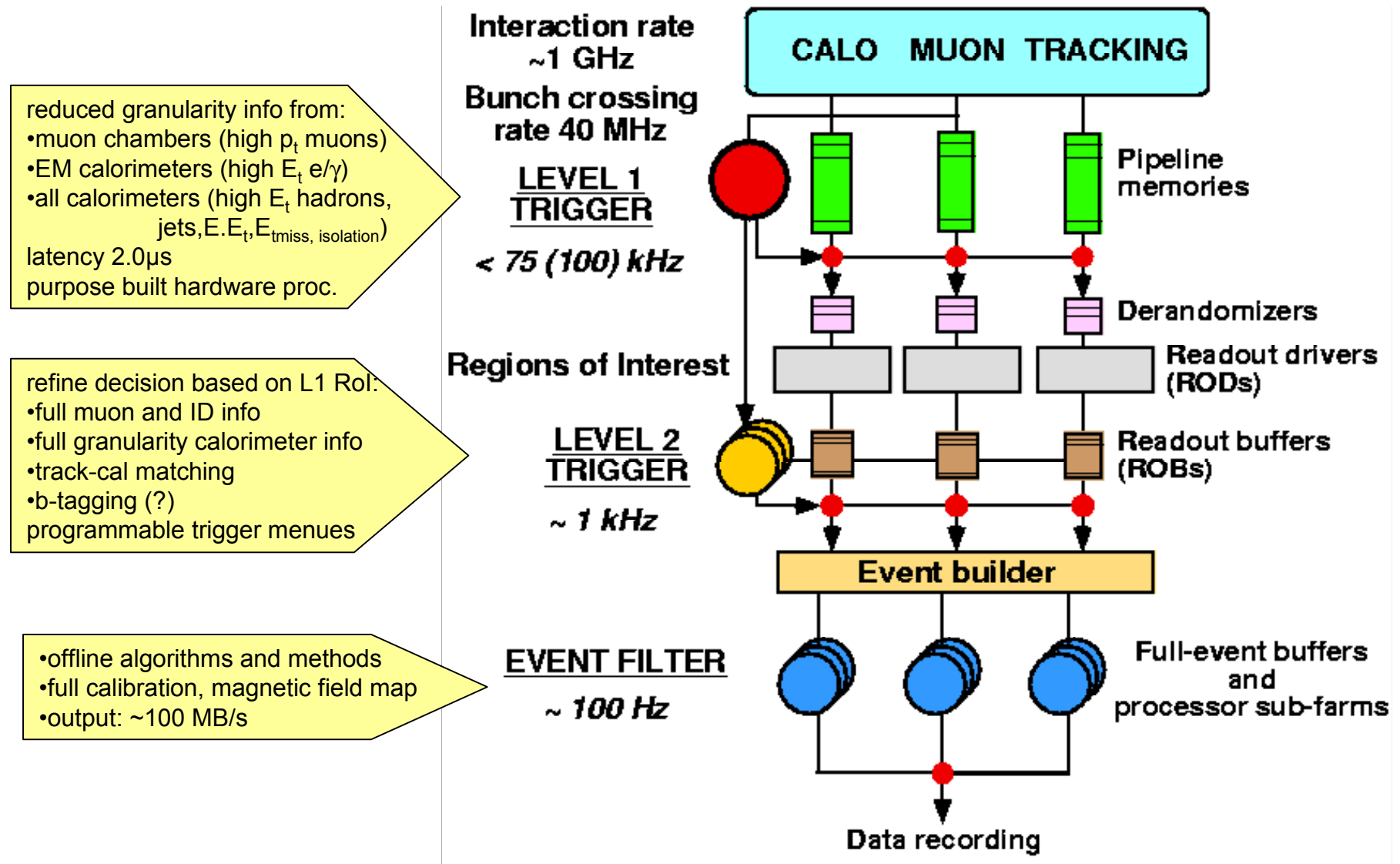
oxygenated material



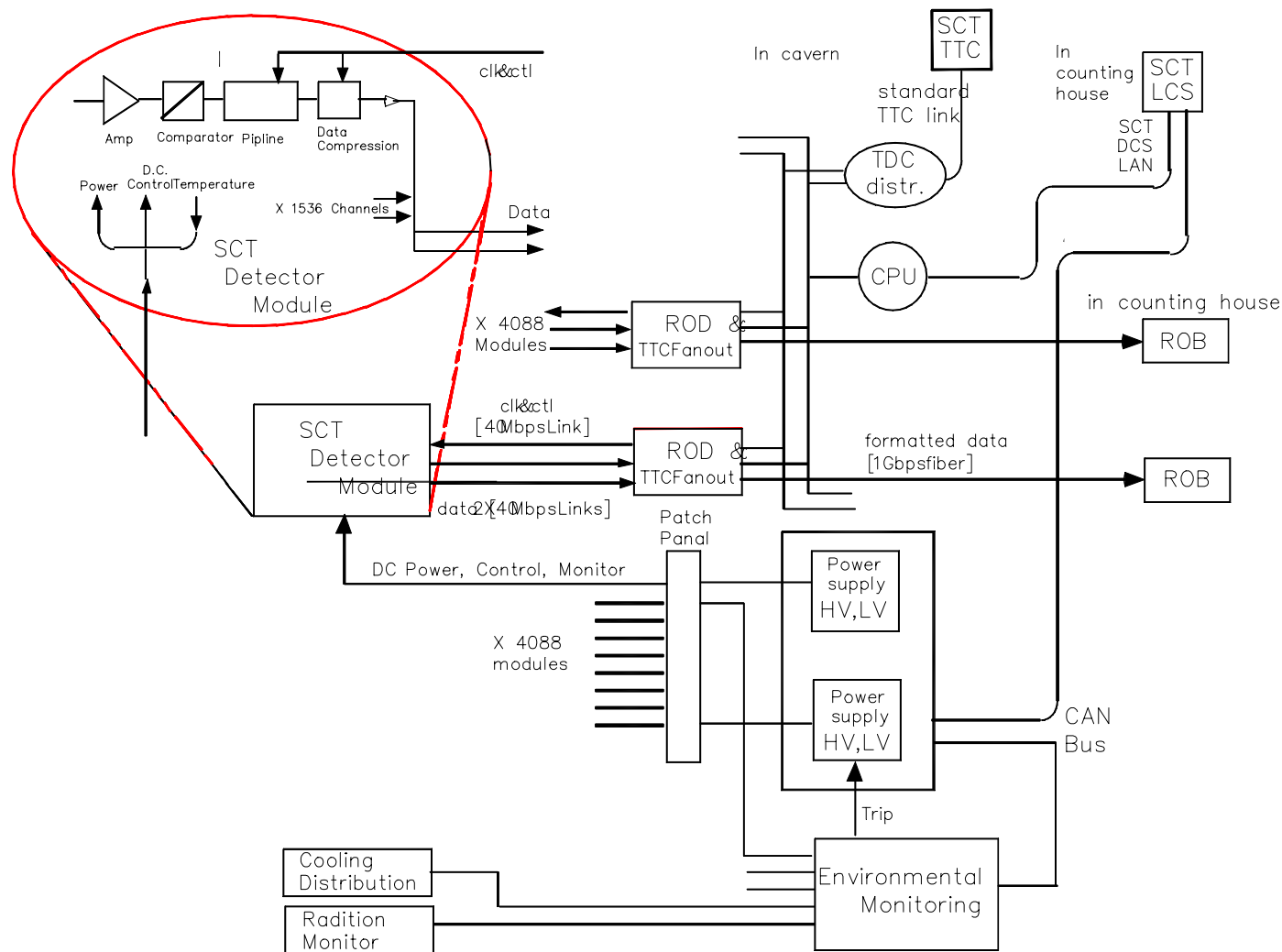
signal seen on single strip with ~20ns shaping after 32 days annealing at 25°C (MPI Munich)



ATLAS Trigger Concept

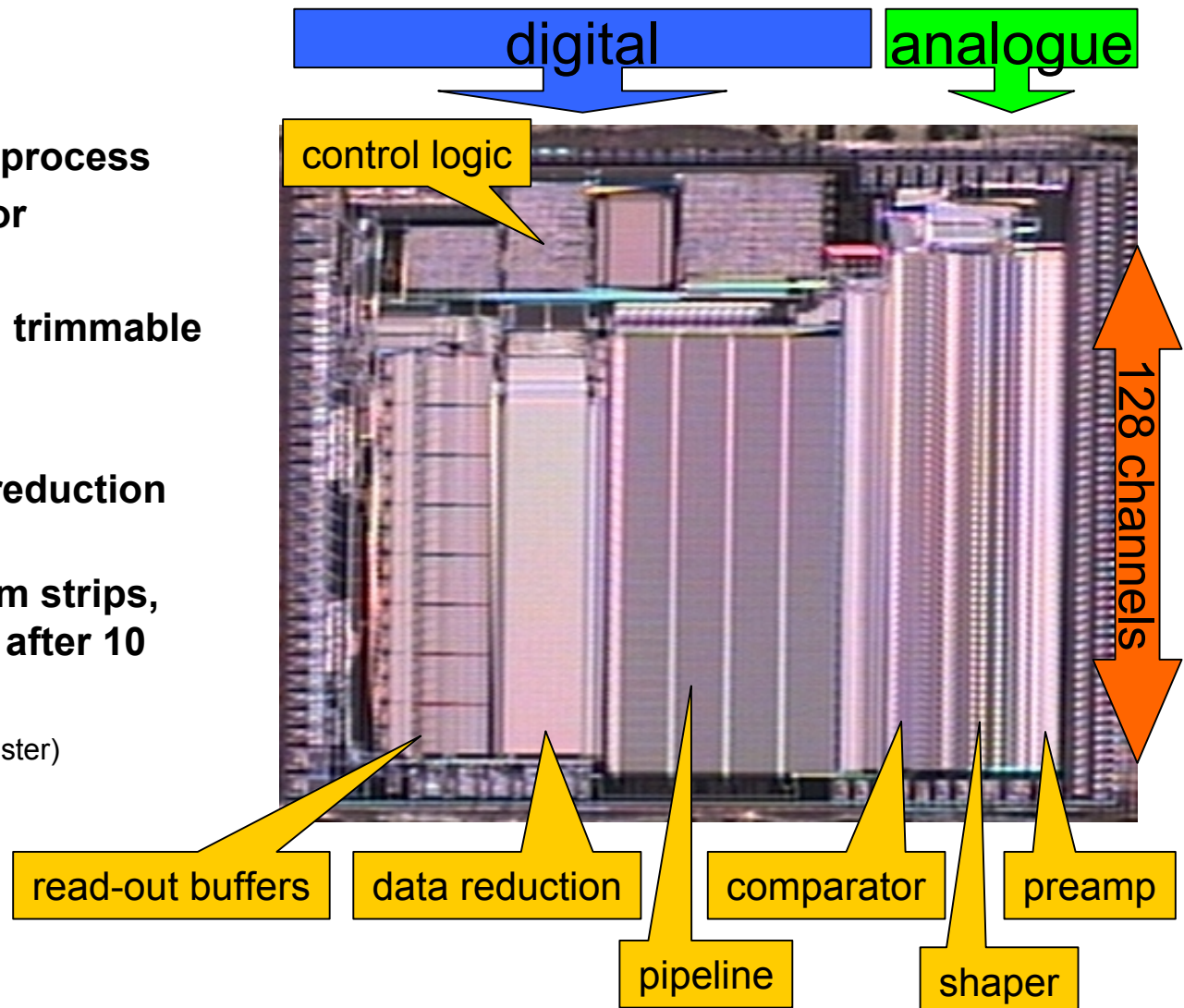


Read-Out Concept



Front-End ASIC ABCD3T

- binary read-out
- 128 channels
- DMILL radiation hard process
- bipolar input transistor
- shaping time ~20ns
- comparator threshold trimmable for each channel
- 132 cell pipeline
- edge detection, data reduction and multiplexing
- ENC ~ 1500 e for 12 cm strips, increasing to ~1800 e after 10 years of irradiation
- 3 mW/channel (3.5 for master)



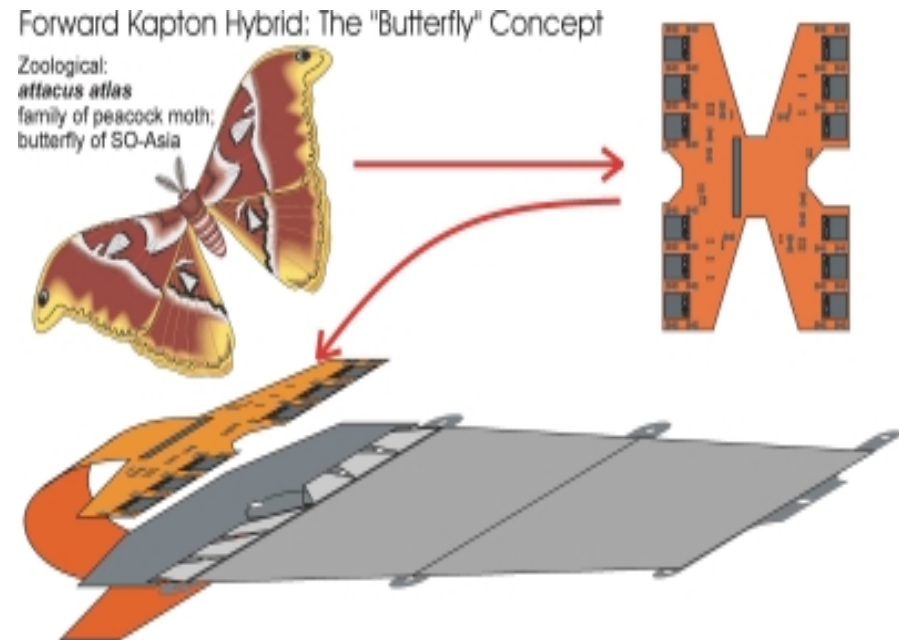
Forward Electronics Hybrid *developed at Freiburg University*

requirements:

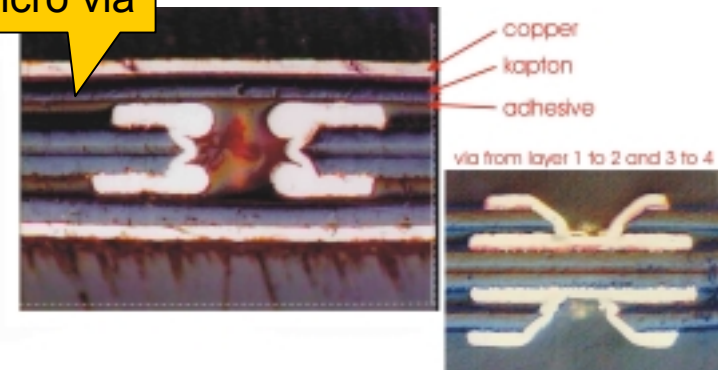
- double sided
- distribute and filter
analogue and digital currents (4V, 1.8A)
- route/filter detector bias (500V)
- filter/shield noise/pick-up
- route commands and data
- full redundancy
- provide electrical/optical connectivity
- remove heat (7.2W)
- low mass

implementation:

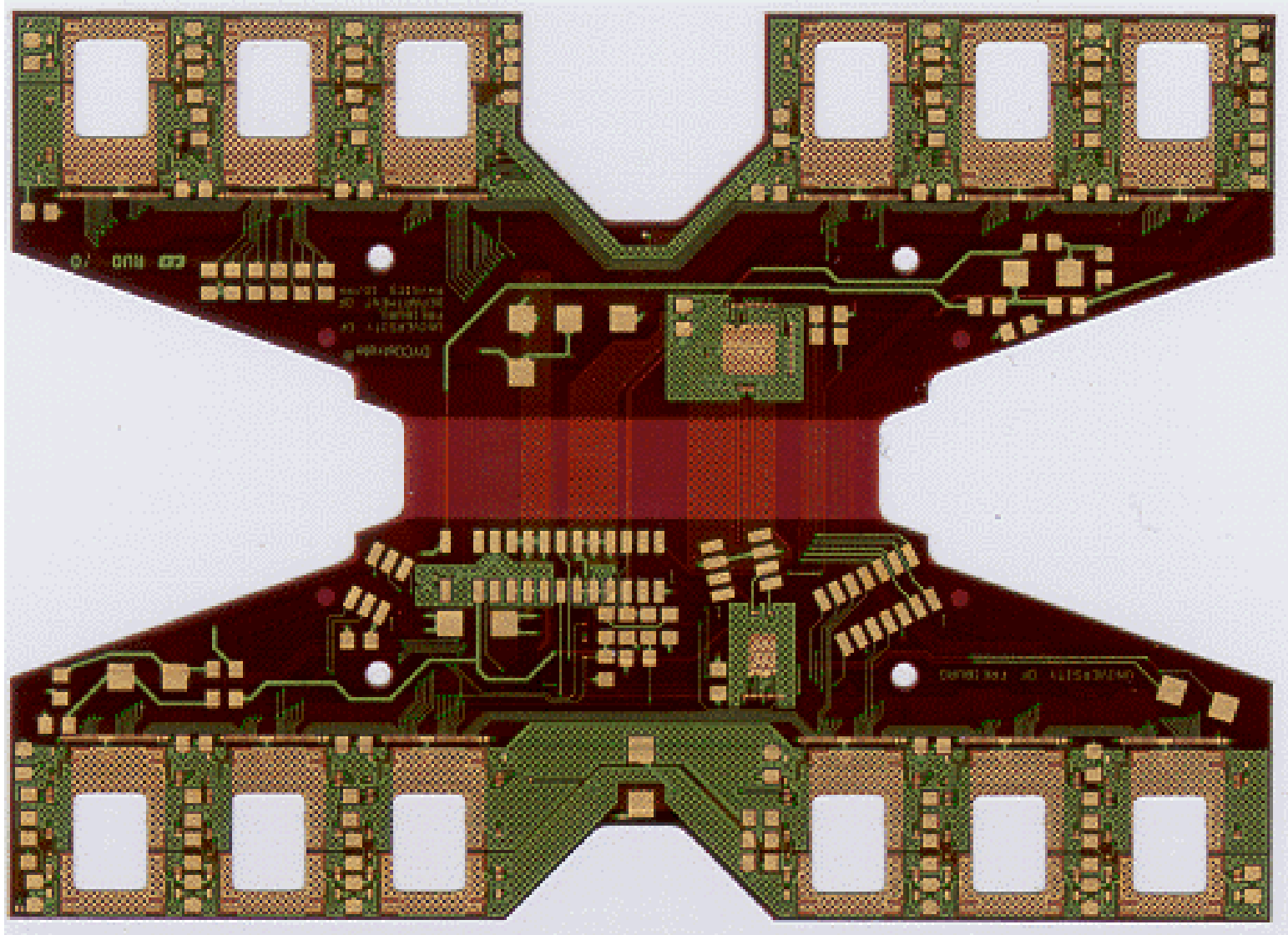
- 4 layers of copper traces in Kapton flex
- trace width/gap $\sim 75\mu\text{m}$
- layer thickness $\sim 15\mu\text{m}$
- ~ 3000 micro vias for connections between planes
- produced at DYCONEX AG
- flex folded around a metallised carbon fibre substrate



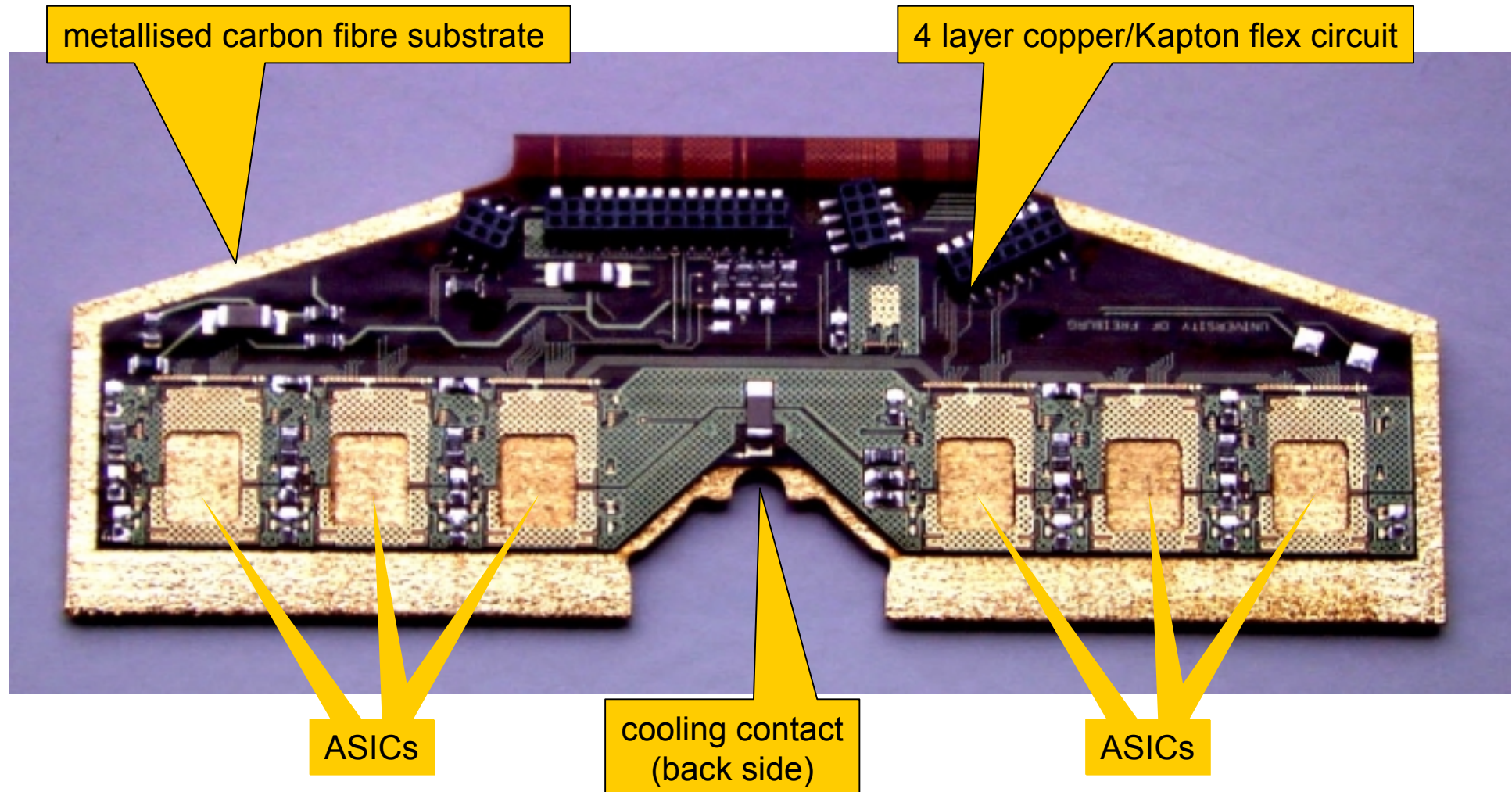
micro via



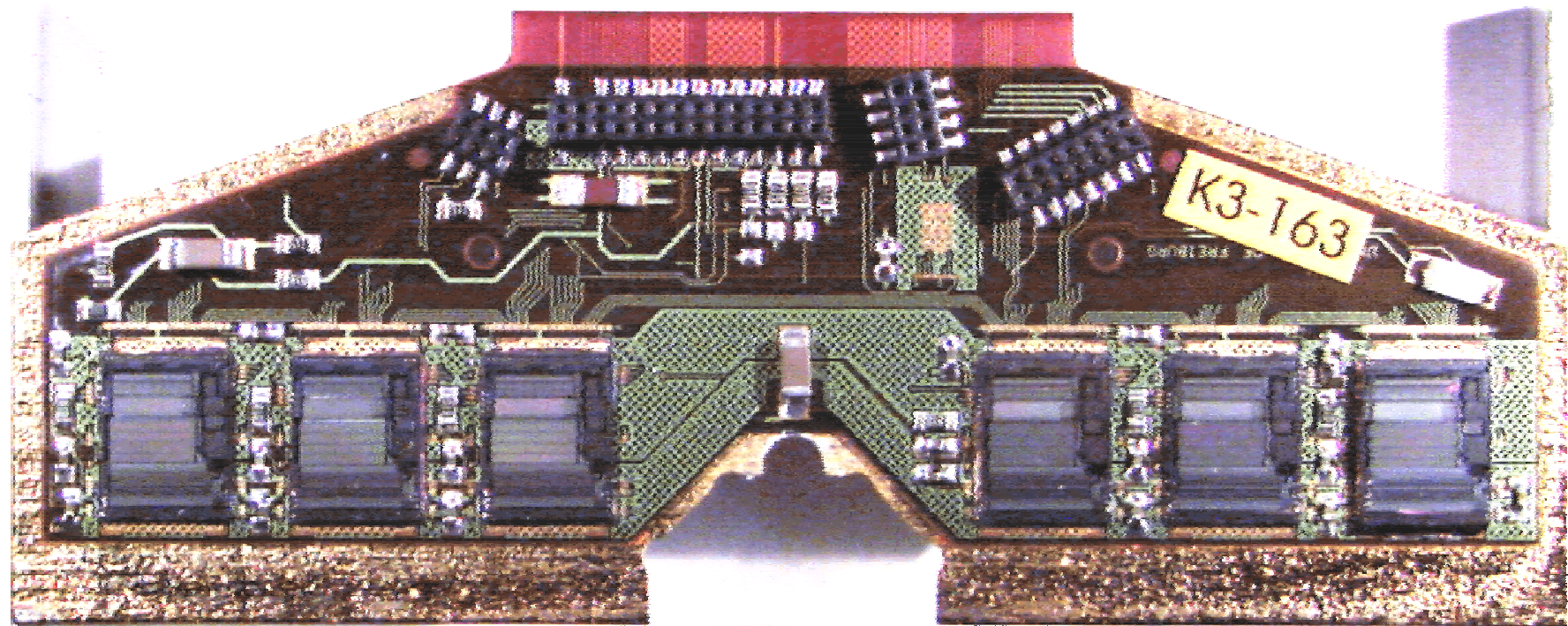
Hybrid Flex Circuit



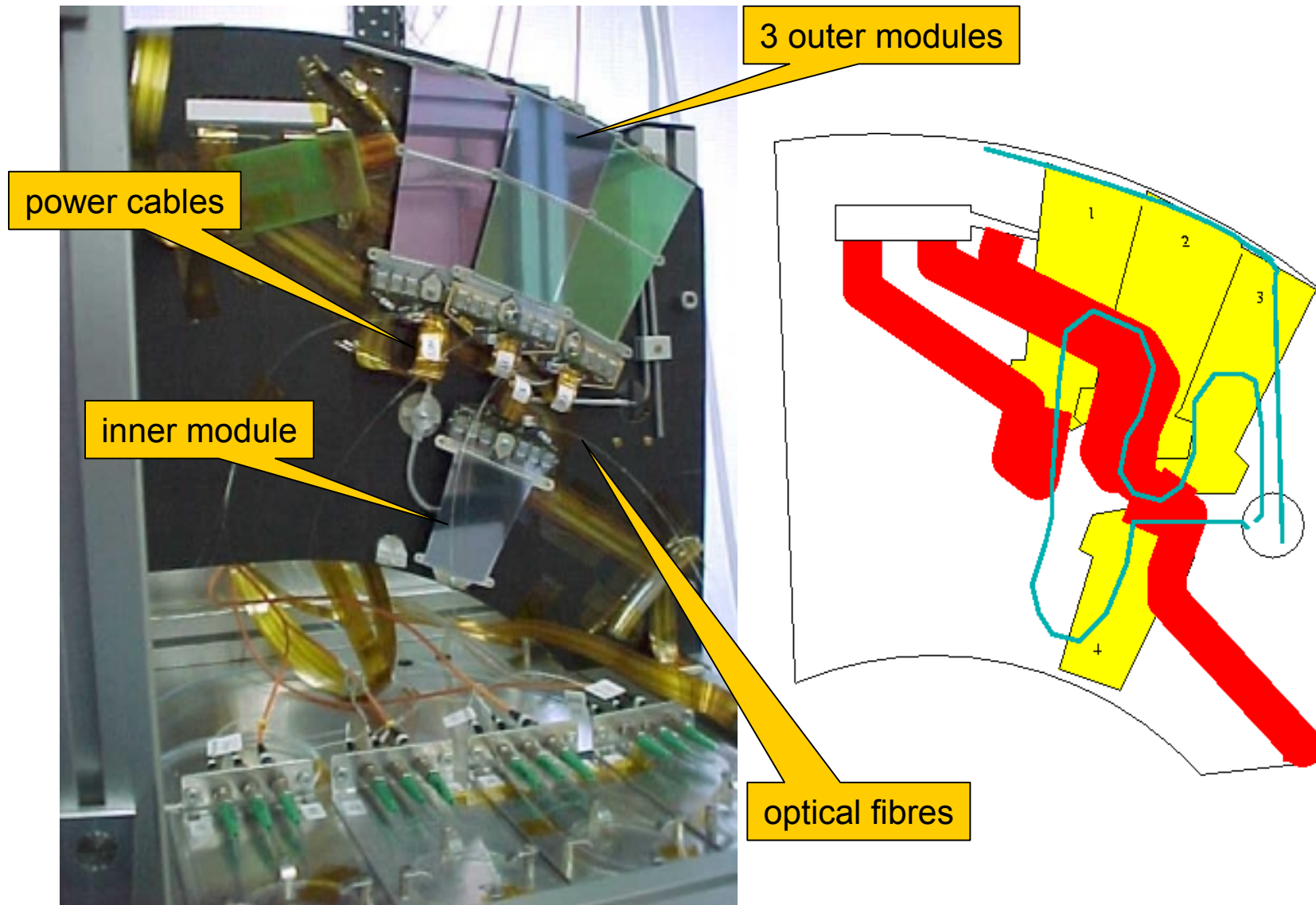
Double Sided Electronics Hybrid (Forward)



Forward Hybrid with ABCD3T Chips



System Test: Forward Mini-Sector



K3-152: Noise on Sector vs. Noise on Bench

$I_{\text{preamp}}=267\mu\text{A}$, $I_{\text{shaper}}=30\mu\text{A}$, $V_{\text{det}}=100\text{V}$, $T_{\text{coolant}}=15^\circ\text{C}$
Compression 01X, Edge Detect On, chips trimmed at 2 fC

Bench:

Run 1786.1,
SCTLV2,
no choke,
conventional cable used.
“Output noise” ~ 12-14 mV

Chip	M0	S1	S2	S2	S4	E5
Gain (mV/fC)	58	57	56	57	55	53
Noise (ENC)	1500	1500	1484	1464	1460	1530

Chip	M8	S9	S10	S11	S12	E13
Gain (mV/fC)	54	52	56	55	56	58
Noise (ENC)	1545	1455	1483	1517	1477	1495

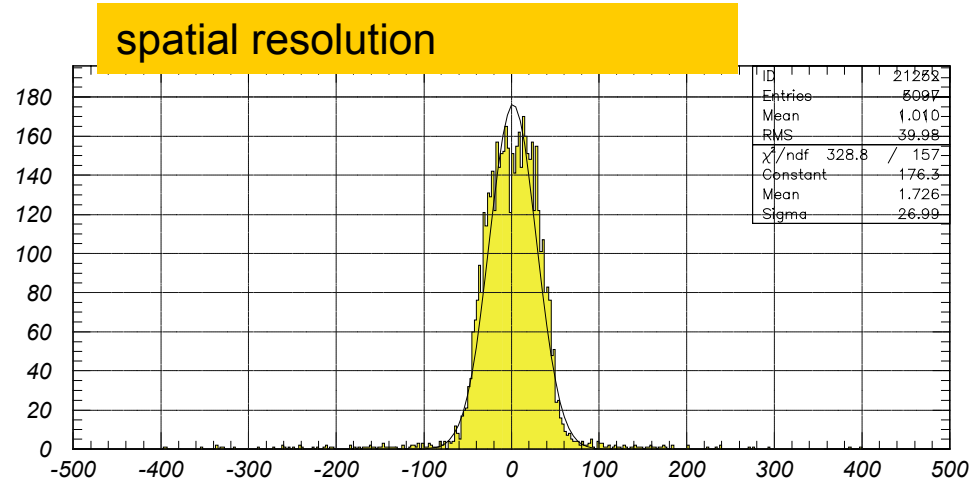
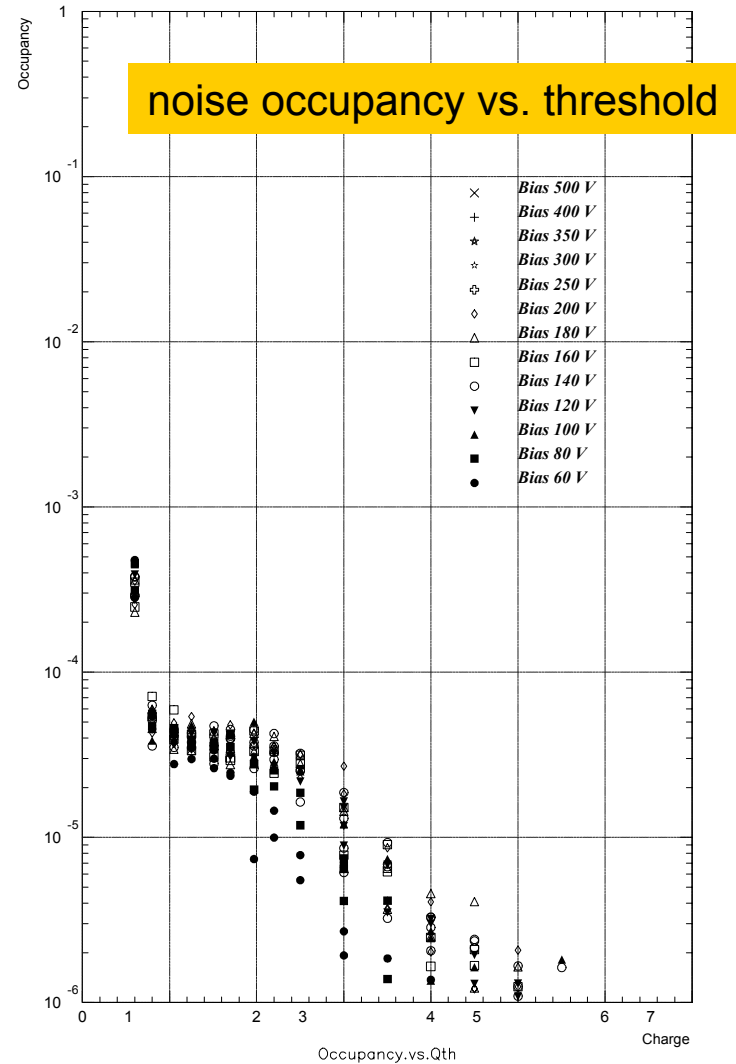
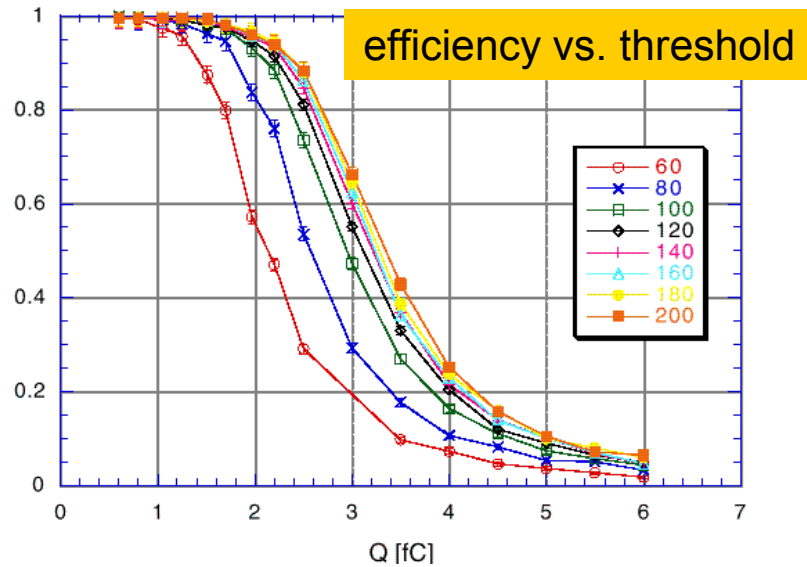
Sector:

Run 825.1,
choke at SCTLV2,
all PPF1 connections made,
module in position 3.
“Output noise” ~ 13-15 mV

Chip	M0	S1	S2	S2	S4	E5
Gain (mV/fC)	62	60	59	62	63	59
Noise (ENC)	1525	1505	1451	1409	1415	1525

Chip	M8	S9	S10	S11	S12	E13
Gain (mV/fC)	62	59	62	59	60	63
Noise (ENC)	1489	1419	1436	1493	1435	1469

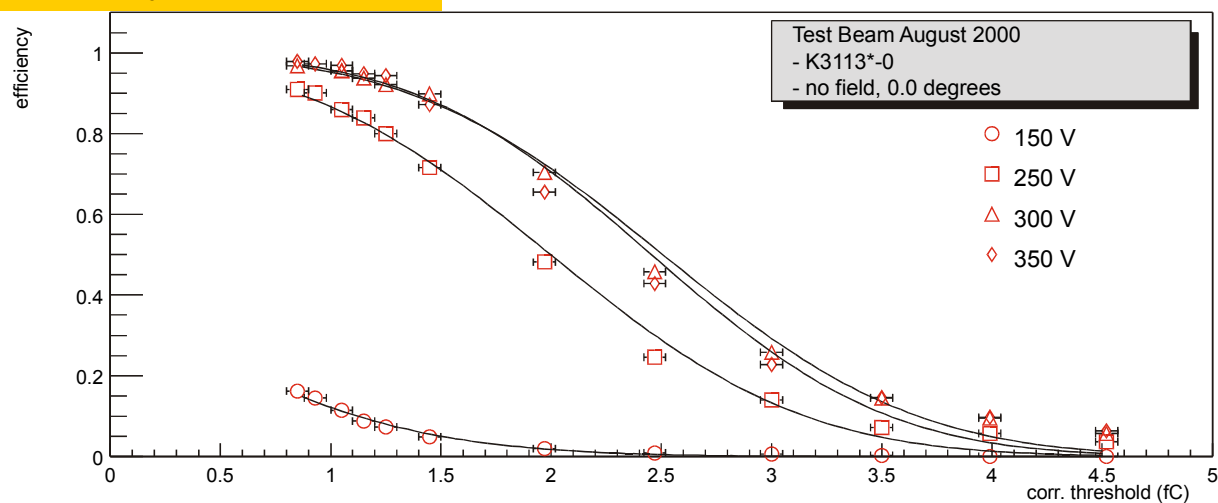
Testbeam Results



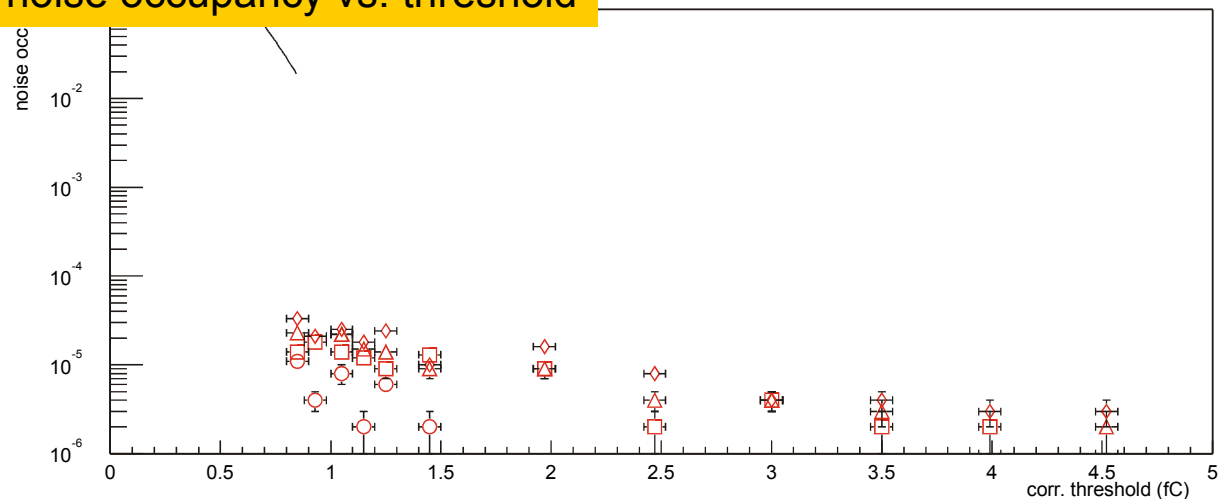
analysis: N. Unno
PRELIMINARY

Testbeam Results on Irradiated Detectors

efficiency vs. threshold

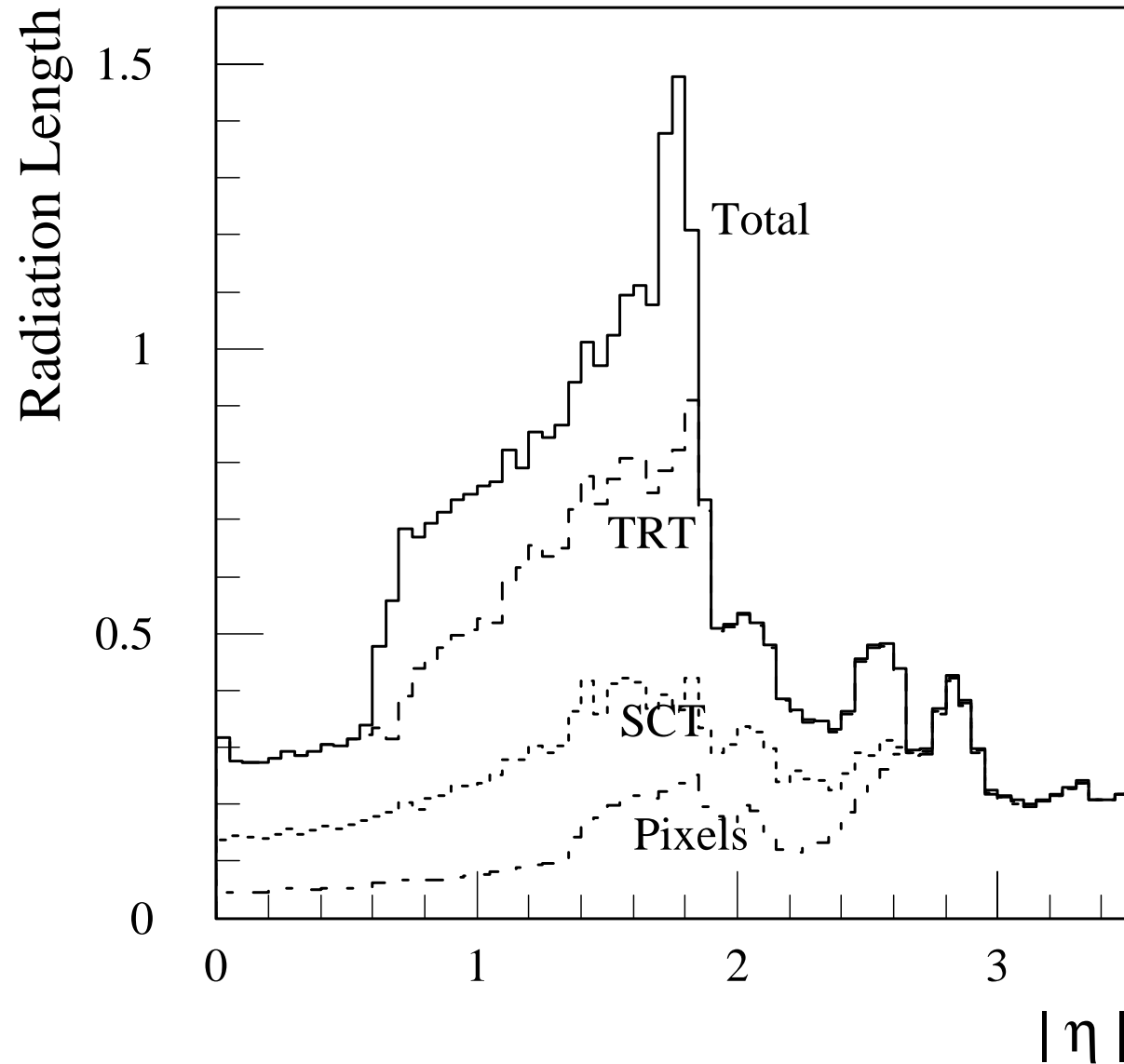


noise occupancy vs. threshold

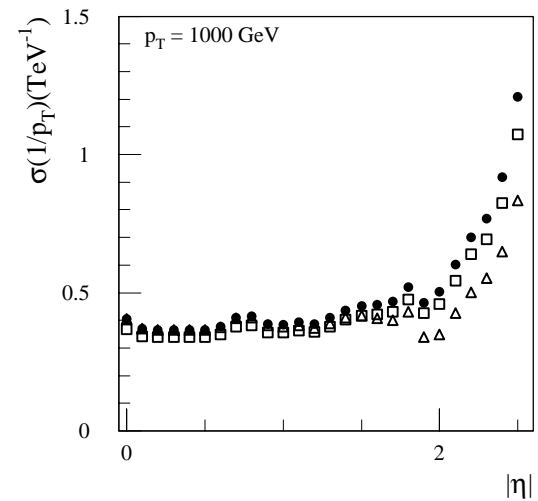
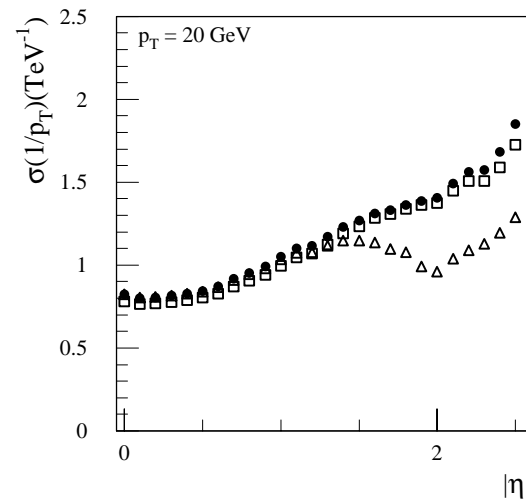
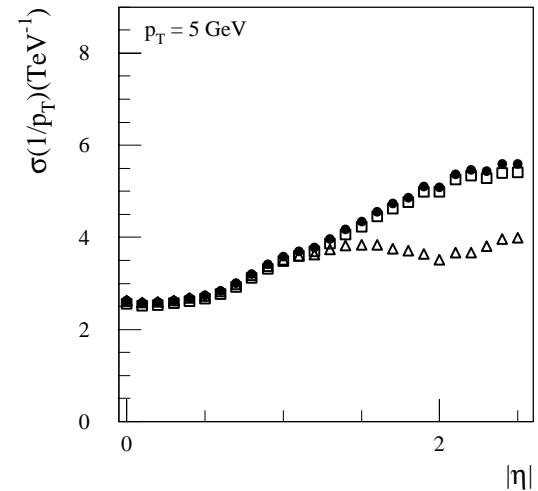
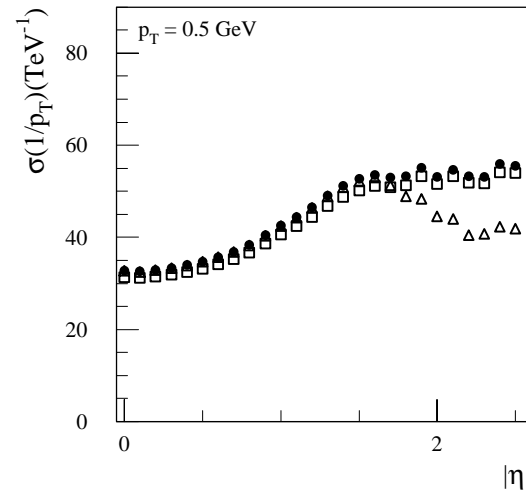
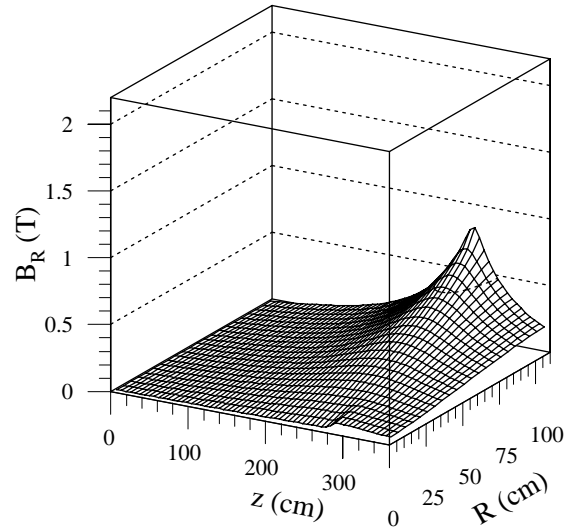
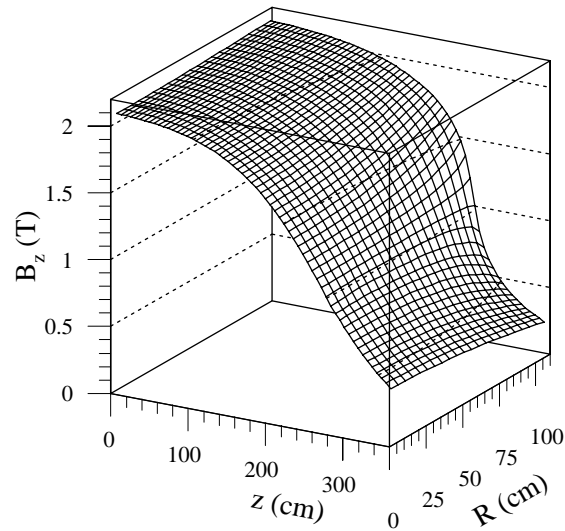


analysis: M. Vos
PRELIMINARY

SCT Material Budget

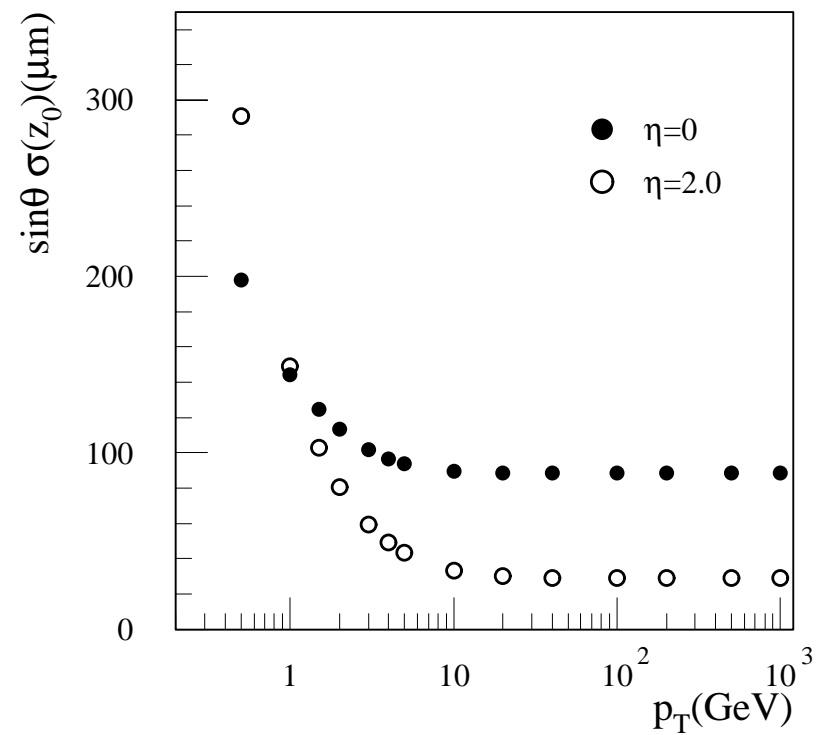
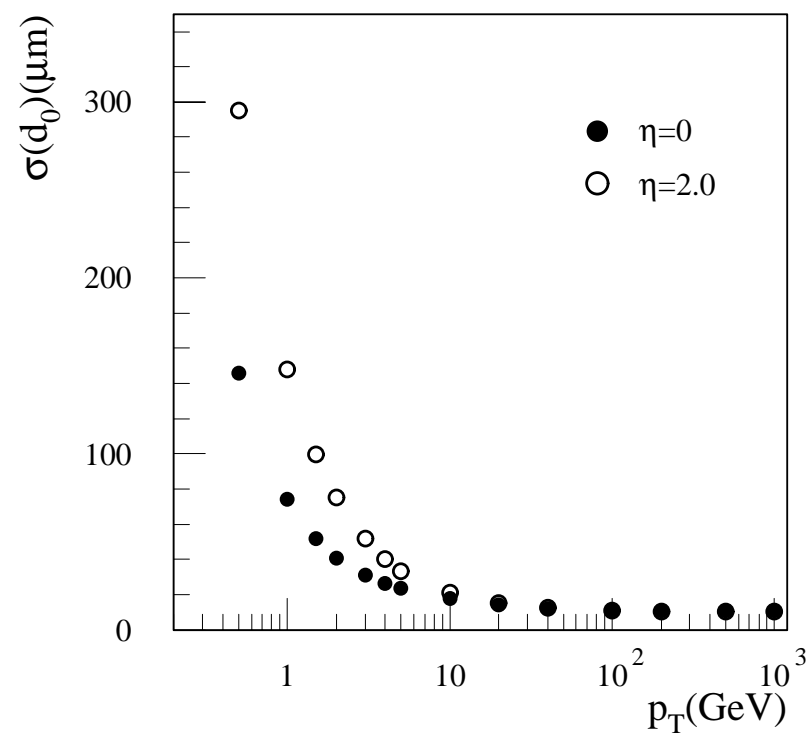


Magnetic Field and p_t Resolution

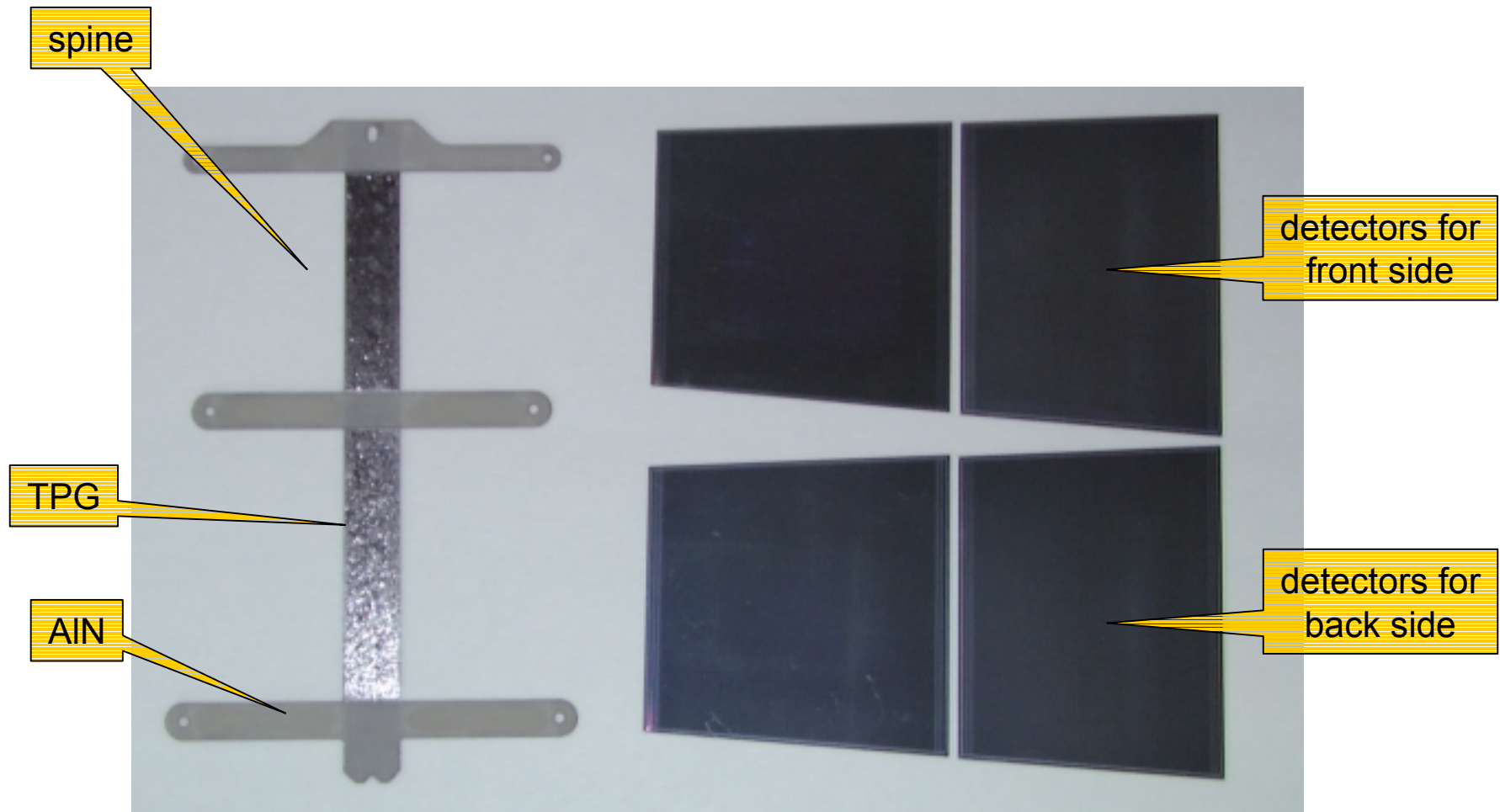


- p_t resolution as a function of $|\eta|$ for muons of various momenta
- circles and squares show simulation for ATLAS solenoidal field, triangles for uniform field

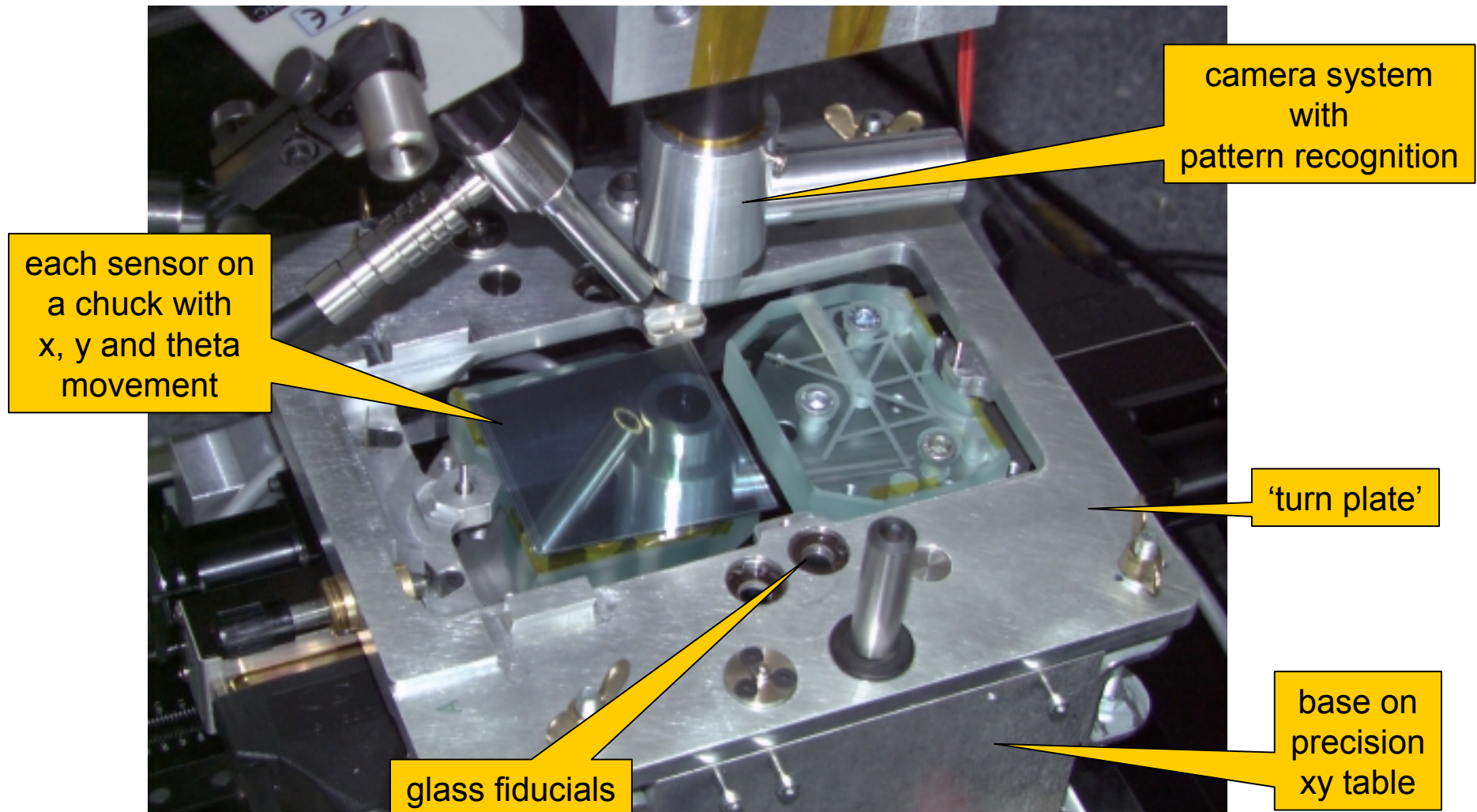
Impact Parameter Resolution



Components for a Detector Module

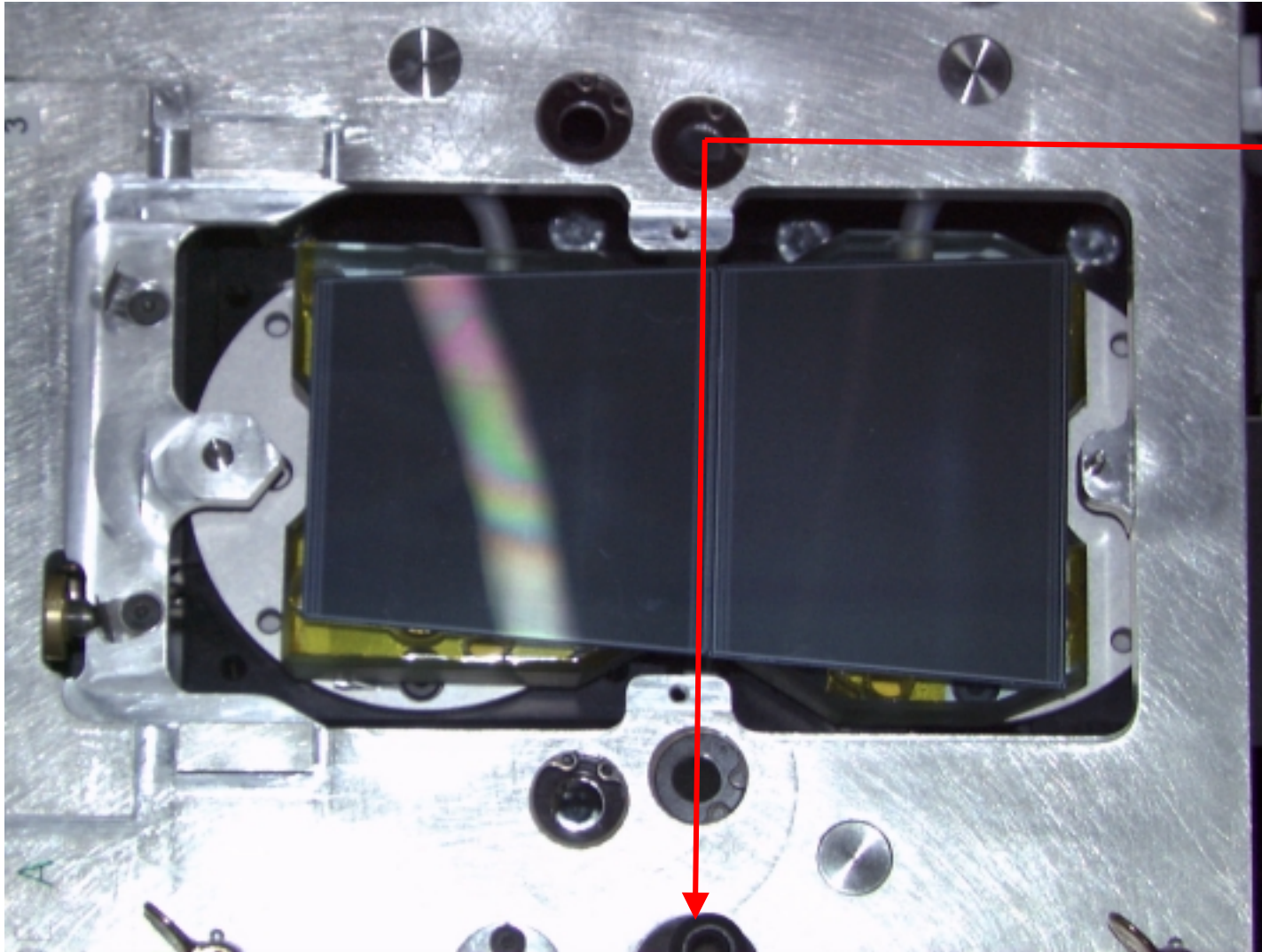


Semi-Automatic Module Assembly

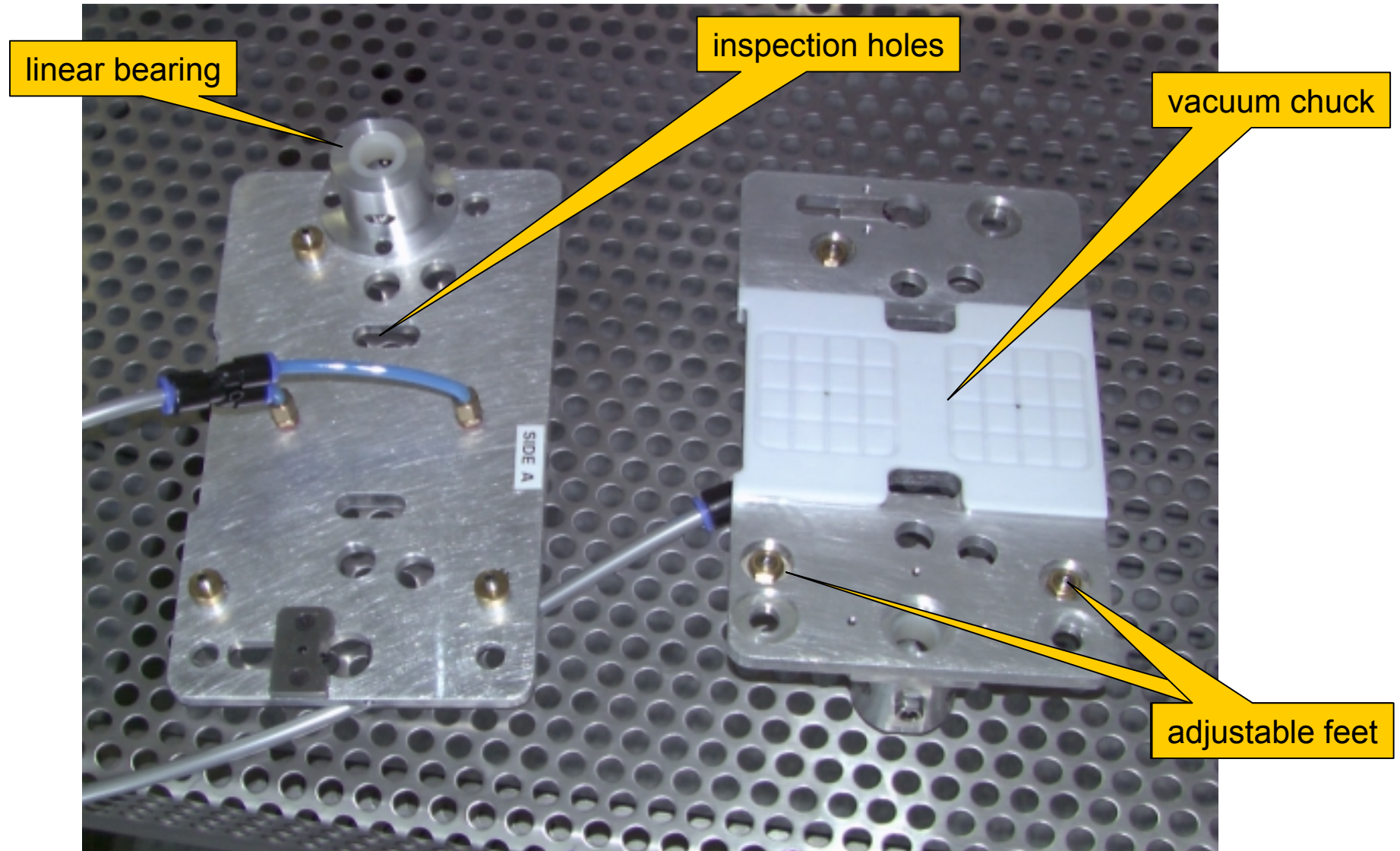


all stages computer controlled (LabVIEW)

Aligned Sensors in 'Turn Plate'



Transfer Plates

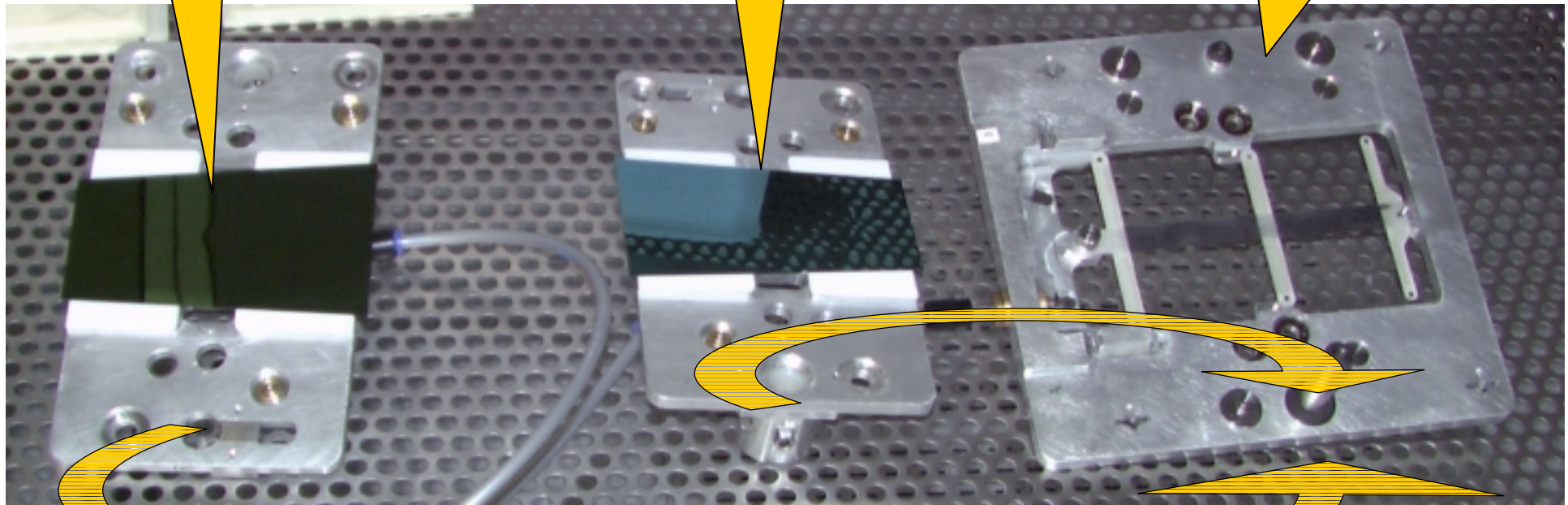


Aligned Pieces ready for Assembly

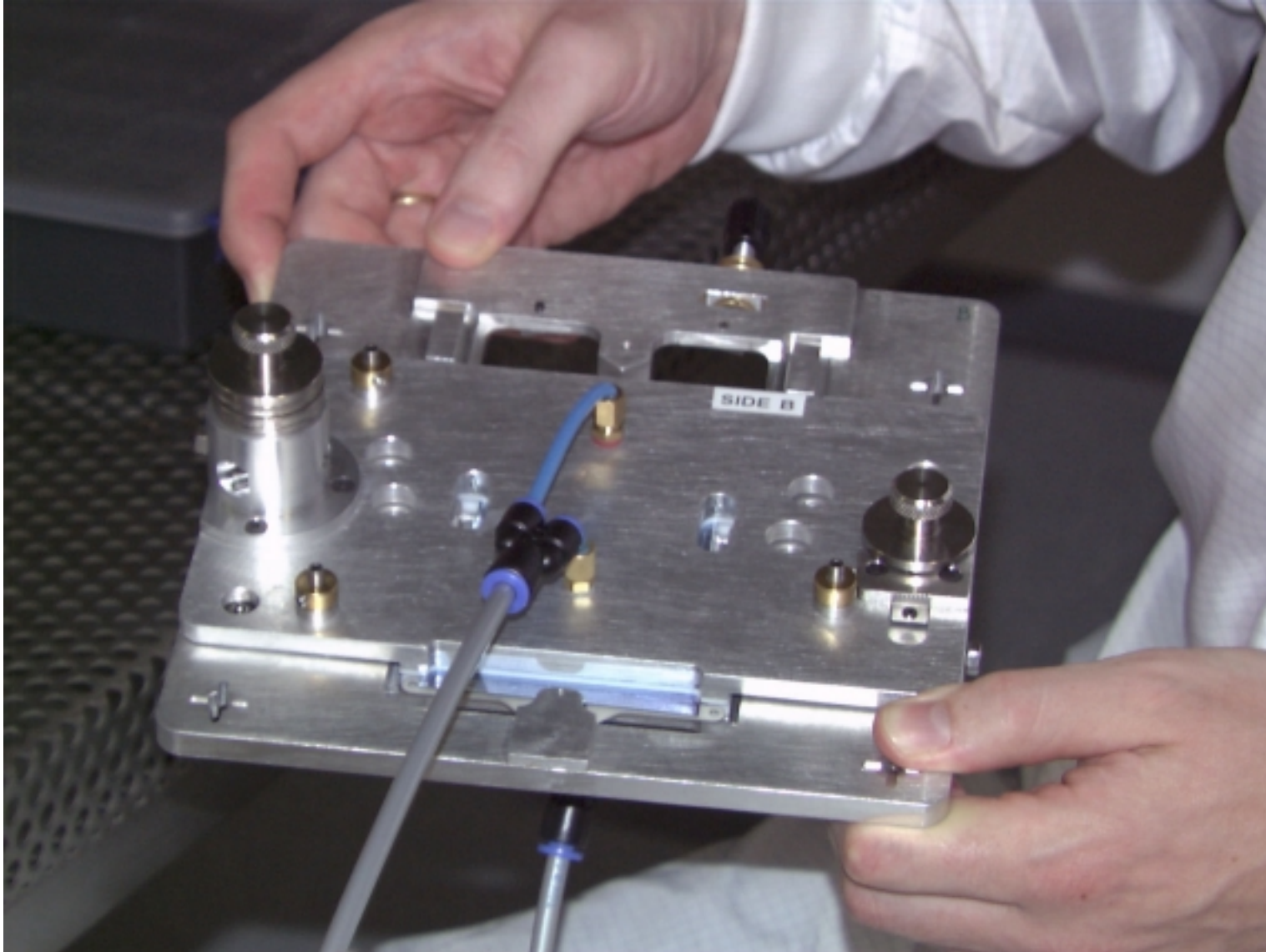
pair of sensors for
back side

pair of sensors for
front side

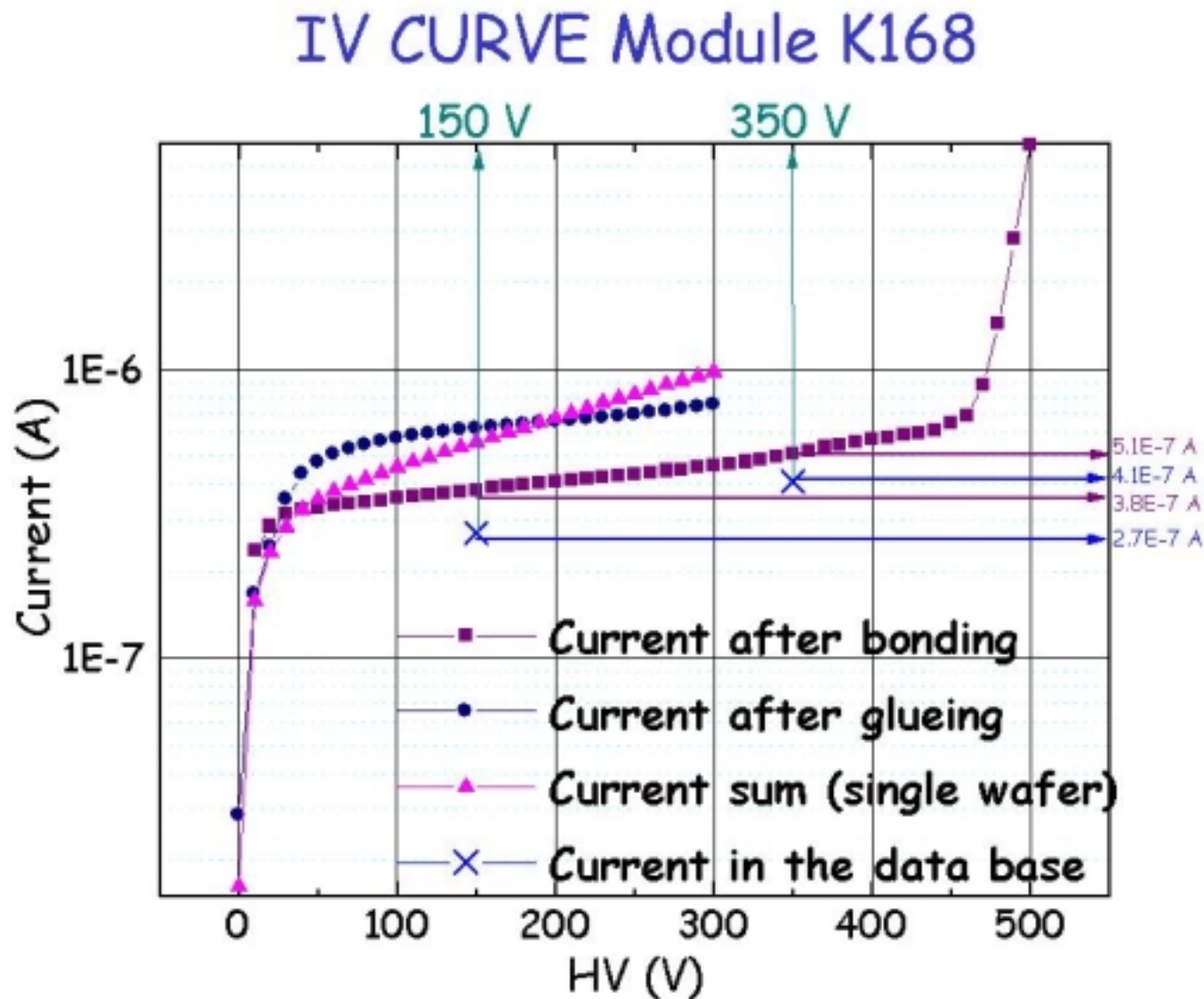
'turn plate' with
'spine' on which
glue has been dispensed



Assembly is finished



Leakage Current before and after Assembly



Metrology: Measurement Microscope

LEICA VMM200
2 μ m accuracy
in x,y,z

computer controlled
metrology using
pattern recognition

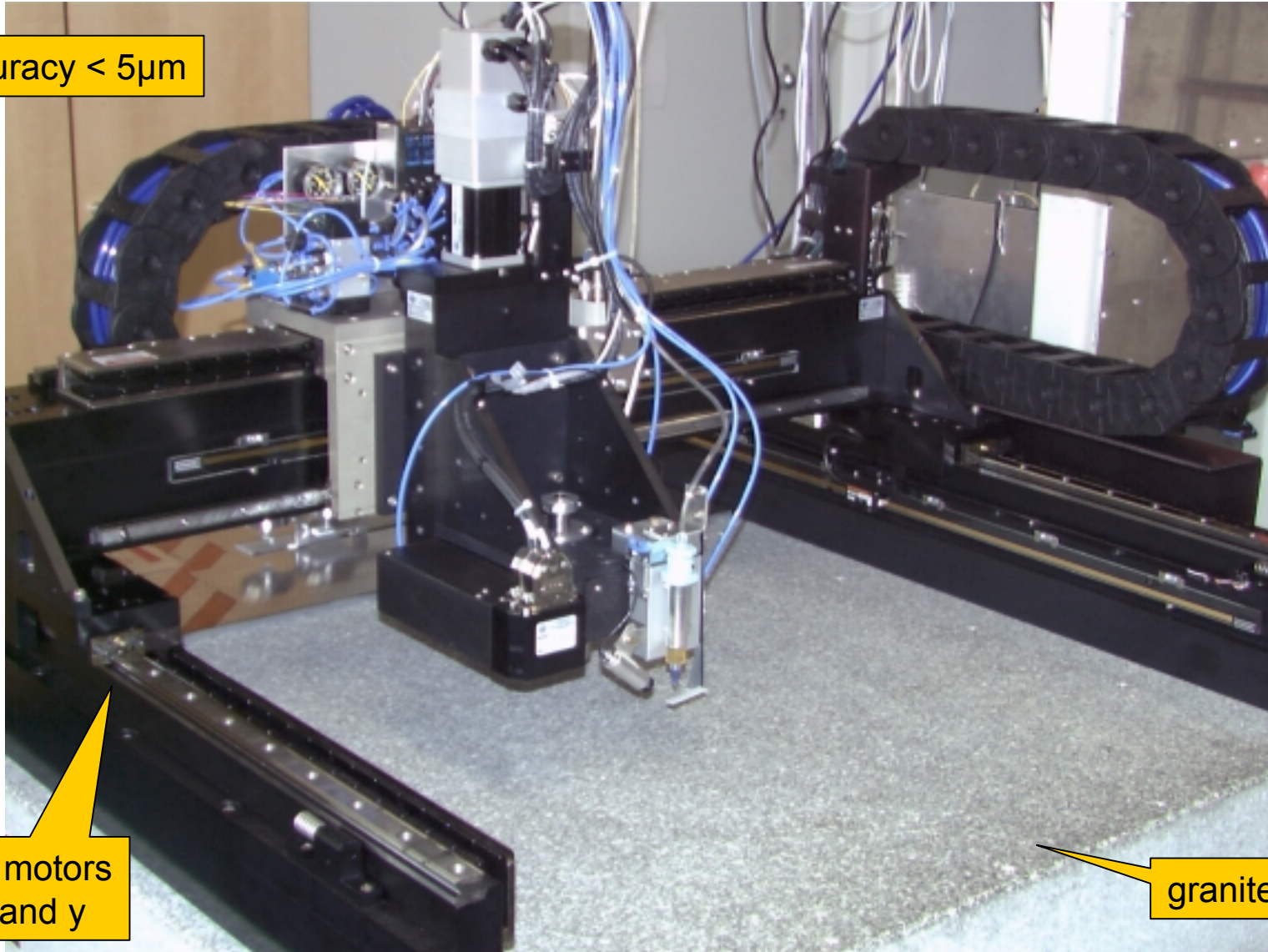


Automatic Assembly Robot

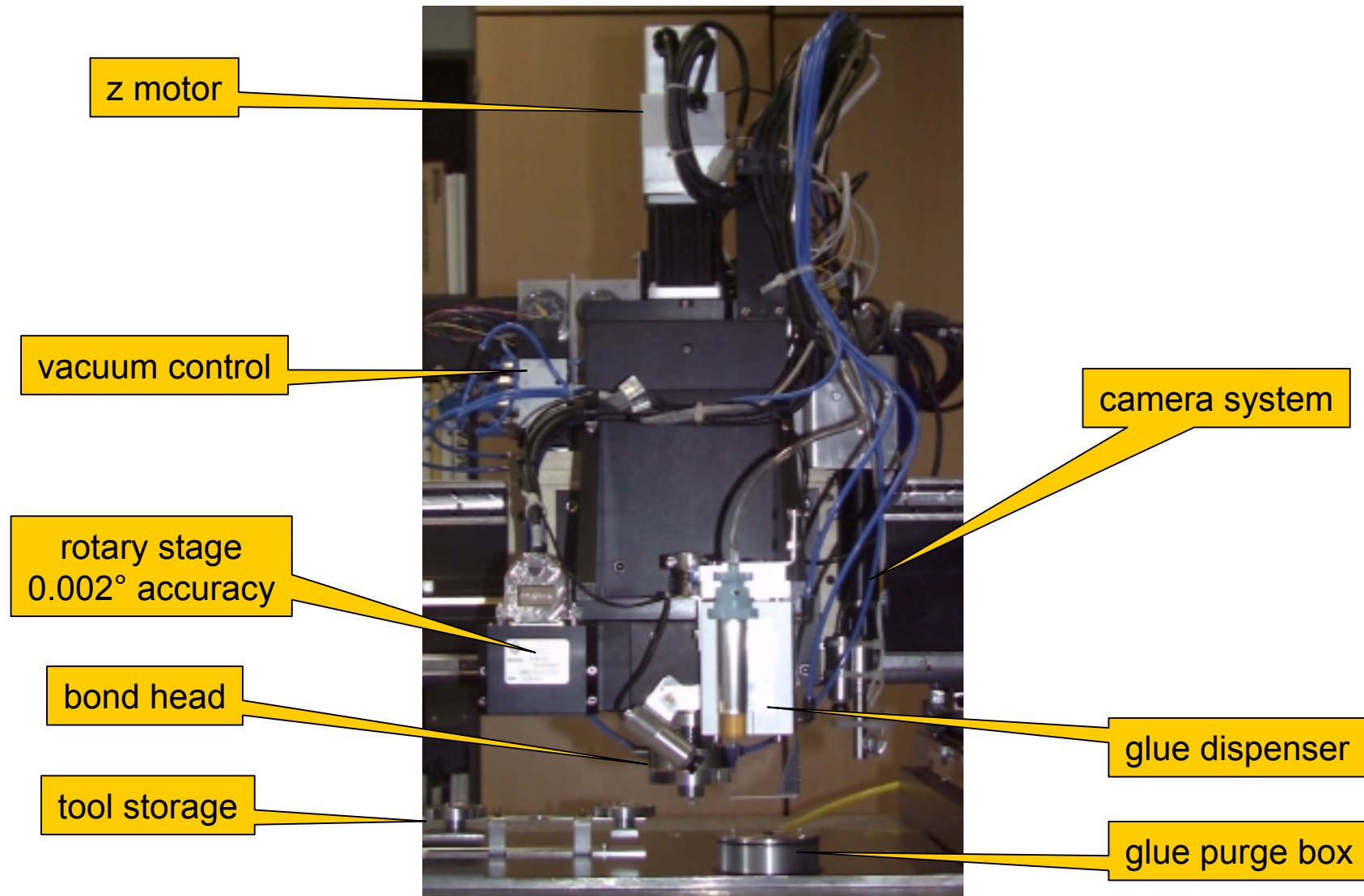
accuracy $< 5\mu\text{m}$

linear motors
in x and y

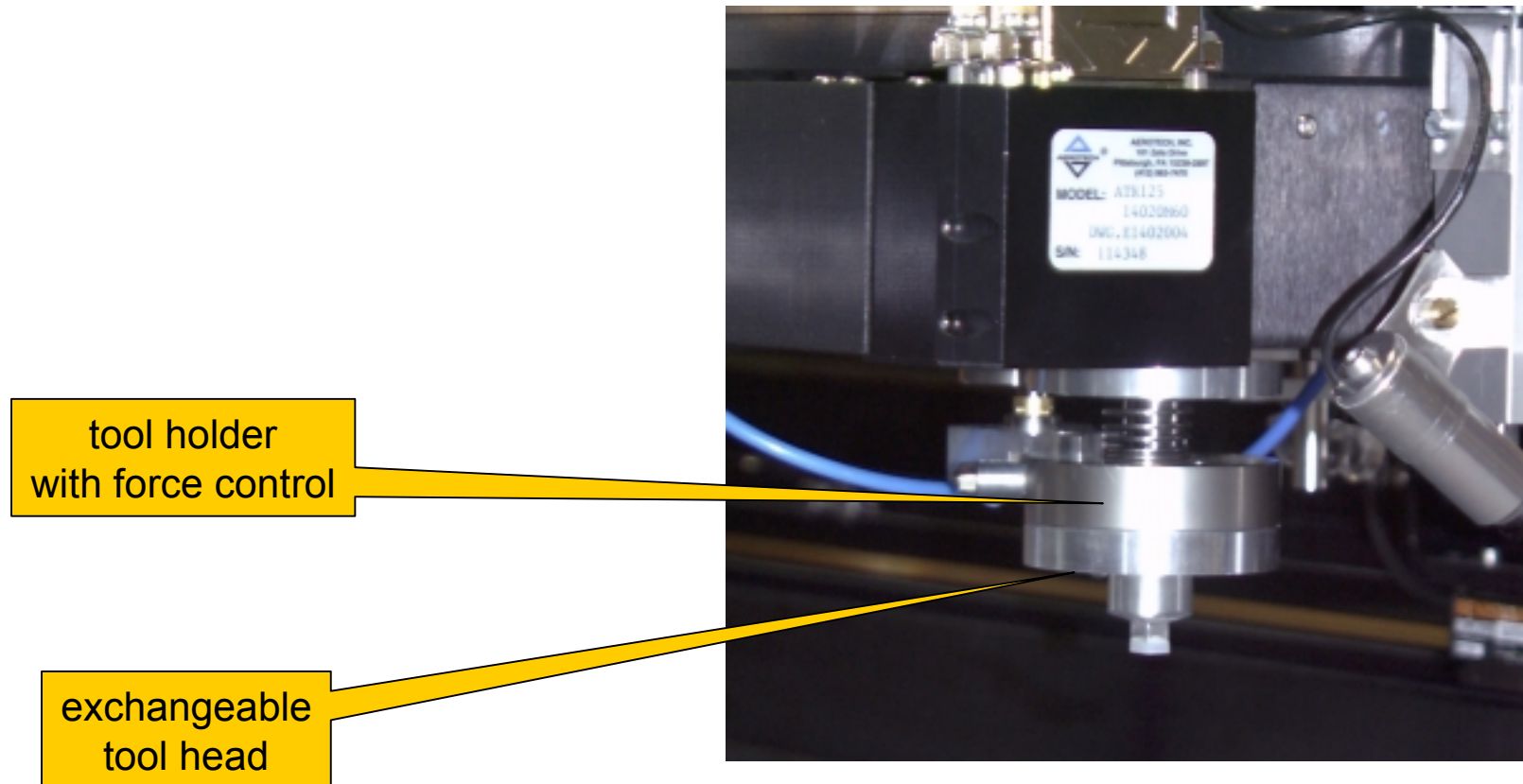
granite base



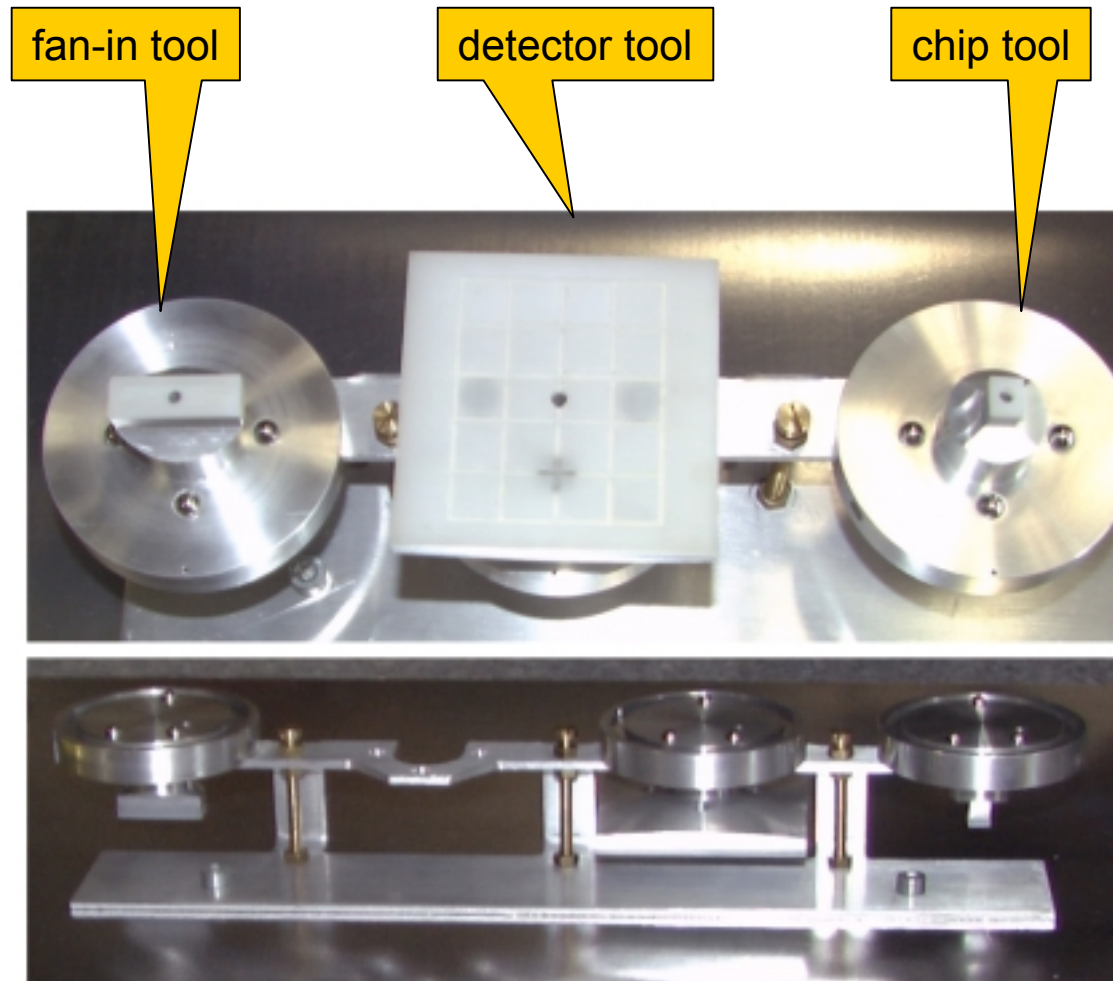
Assembly Head



Bond Head



Tool Heads



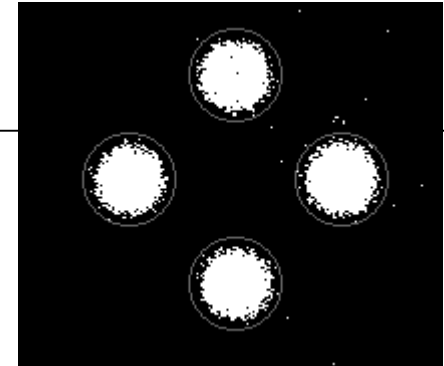
Repeatability

measurement in xy:

random run with 20 cm diameter and a speed of 5 m/min

->repeatability in x,y < 1 μm

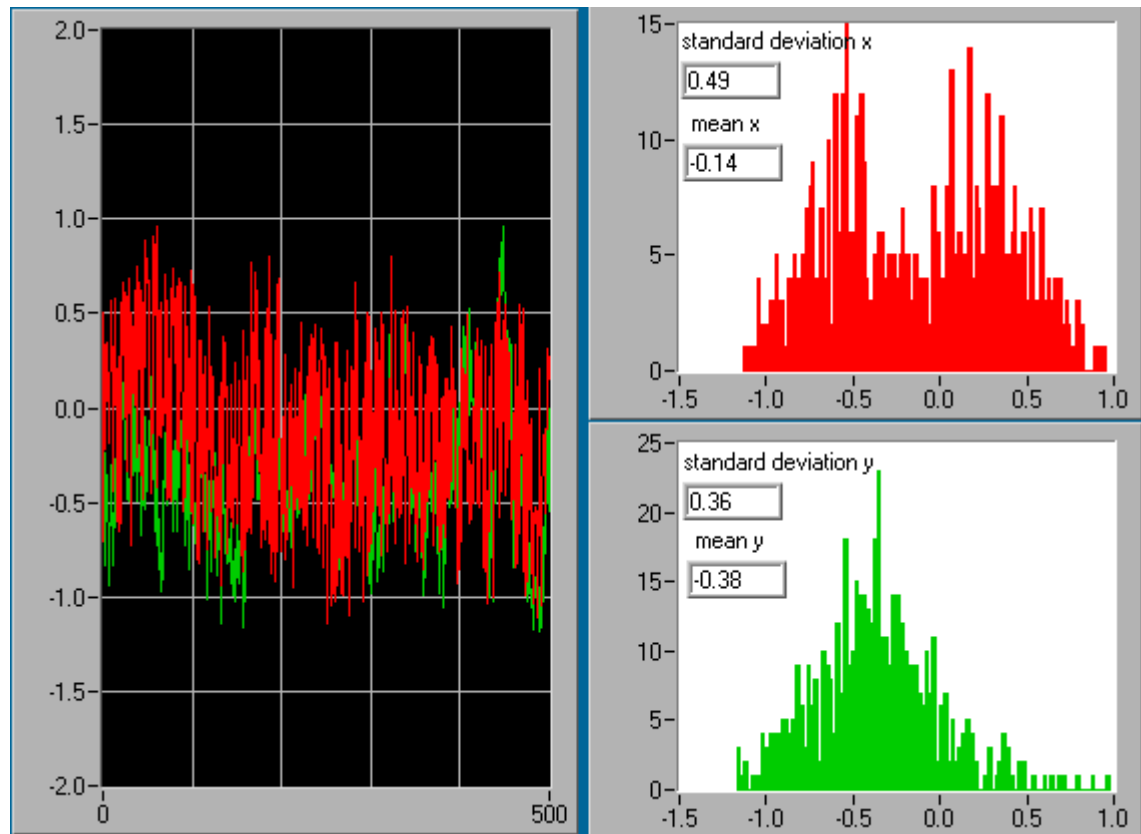
fiducial



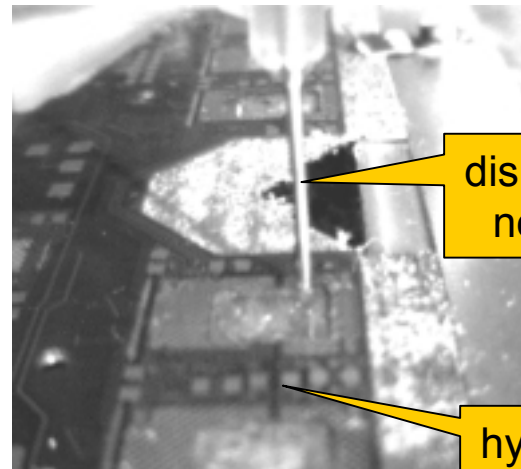
rotation:

using laser setup

->repeatability 0.002°

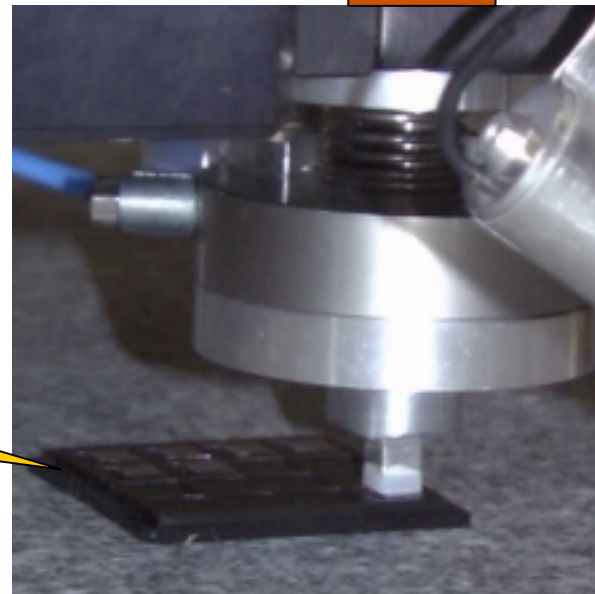
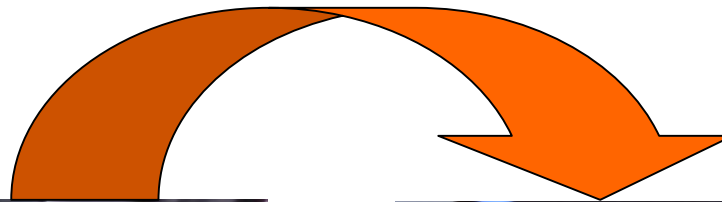


Glue Dispensing and Placement of Chips on a Hybrid

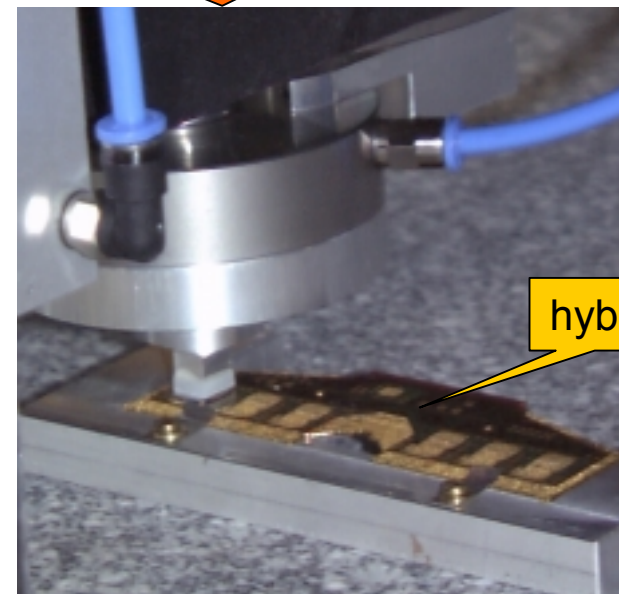


dispenser
needle

hybrid



chips in
storage box



hybrid

Summary and Current Status

- the ATLAS SCT is now **preparing the production phase**
- **sensors** are under fabrication
- **front-end electronics** chosen and starting pre-production
- electronics **hybrids** close to final design review
- **module design** close to final design review
- several close-to-final **modules built and tested** (incl. irradiation)
- **module assembly** procedure defined and production centres in qualification step
- **off-detector electronics** and services in prototyping
- **cooling** tested on prototypes
- **barrel support** structure under construction
- **forward support** structure in prototyping

